MAINTENANCE MANUAL RF BOARD 188D5062G2 (403-440 MHz) 188D5062G1 (440-470 MHz) 188D5062G3 (470-512 MHz) 188D5062G4 (485-505 MHz, 12.5 kHz SPACING)

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DESCRIPTION

The RF Board for the MDX radio consists of the following circuits:

- A frequency synthesizer for generating the transmit carrier frequency and the receive circuit first mixer injection frequency
- The transmit exciter, PA and power control stages
- The receive circuit front end, IF and FM detector
- Voltage regulators

The 403-512 MHz range of UHF frequencies is covered by four groups of RF Boards:

- 1. 188D5062G2: 403-440 MHz
- 2. 188D5062G1: 440-470 MHz
- 3. 188D5062G3: 470-512 MHz
- 4. 188D5062G4: 485-505 MHz, 12.5 kHz spacing

The RF Board is mounted in the bottom of the frame assembly. Refer to the Combination Manual for the mechanical layout of the radio. Figure 1 provides a block diagram of the receive and transmit circuits. Figure 2 provides a block diagram of the synthesizer.

Transmit circuit adjustments for frequency, power and deviation are accessible form the topside of the board, as are IF alignment, second oscillator and audio level adjustments for the receive circuit. Chip components on the bottom of the board provide optimum RF performance, while being accessible for easy servicing by removing the "friction fit" bottom shields.

Selected use of sealed modules permits small board size as well as RF and mechanical protection for sensitive circuitry. Modules are not repairable and must be replaced if they are determined to be damaged.

Ericsson Inc.

Private Radio Systems Mountain View Road Lynchburg, Virginia 24502 1-800-528-7711 (Outside USA, 804-528-7711)



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CIRCUIT ANALYSIS

SYNTHESIZER CIRCUIT

The synthesizer circuit generates all transmit and receive RF frequencies for the MDX Conventional mobile radio. This circuit uses a phase-locked VCO module (U201), feeding a doubler circuit to generate the transmit RF operating frequency.

While transmitting, the VCO operates at 1/2 the actual transmitter frequency (201.5-256.0 MHz to produce 403-512 MHz).

While receiving, the VCO operates at 1/2 of the difference between the receive frequency and the 45 MHz IF (179.0-233.5 MHz for 403-512 MHz).

Transistor Q201 doubles the VCO output frequency with input and output filters broadly fixed tuned to allow the VCO second harmonic to pass, while rejecting all other frequencies. The doubled signal is amplified by Q201 to a level of +10 dBm. This signal feeds the receive circuit first mixer and is attenuated to +3 dBm by resistor R202 to feed the transmit exciter module.

The synthesizer frequency is controlled by a microprocessor located on the Audio/Logic Board. Frequency stability is maintained by a Temperature Compensated (X)crystal Oscillator (TCXO) module. The oscillator has a stability of ± 2.5 PPM (0.00025%) over the temperature range of -30°C to +60°C and determines the overall frequency stability of the radio.

The VCO output is also buffered by transistor Q204 to feed the divide by 128/129 dual modulus prescaler U205. The prescaler feeds the FIN input of Phase-Lock-Loop (PLL) U206. Inside of U206, the prescaled signal is further divided down to 6.25 kHz or 5 kHz to be compared with a reference signal. This reference signal is derived from the 12.8 MHz of TCXO module U204. PLL U206 divides the 12.8 MHz TCXO frequency down to the 6.25 kHz or 5 kHz reference frequency.

Divider circuits in U206 are programmed by three inputs from the Audio/Logic Board, which are buffered and inverted by transistors Q208, Q209 and Q210. The S ENABLE pulse (5 milliseconds) activates switch U202 to more rapid channel acquisition during channel changes. A LOCK DET signal from the PLL goes to the microprocessor for processing to prevent transmission when the VCO is not on frequency and to provide an error message to the user. During receive, an unlocked synthesizer is indicated by **SYN** LOCK displayed in the LED display and by a quick, pulsed alert tone. The microprocessor will continually try to reload the frequency information into the PLL until the synthesizer locks. During transmit, only a slower pulsed alert tone will be heard. Once unlocked in transmit, the synthesizer will not be reloaded. The transmitter PTT switch must be unkeyed and then keved again to attempt to relock.

Audio modulation from the Audio/Logic Board is applied to the VCO module through **DEVIATION ADJUST** potentiometer R226. **VCO TUNE** potentiometer R218 adjusts the operating frequency range of the VCO by varying a negative bias from diodes D202 and D203.

Low frequency modulation is applied to TCXO U204 through LOW FREQUENCY ADJUST potentiometer R255.

TRANSMIT CIRCUIT

The transmit circuit consists of a fixed-tuned exciter module, a 10 watt PA module, a PIN diode switch, a low pass filter, a directional coupler, a power control circuit and a transmit voltage switch.

Exciter Module

Figure 1 shows the synthesizer driving the receive mixer at +10 dBm and is attenuated by resistor R202 to +3 dBm for driving the exciter input. Exciter module A102 operates from a switched 8 volt supply. A different exciter module is required for each of the three band splits. No tuning is required . Both input and output ports operate at 50 ohms impedance. The exciter module provides typically 20 dB of gain and 200 mW of output power to drive the power amplifier module.

Power Amplifier Module

The PA module U101 requires a drive of 200 mW from the exciter module to deliver up to 10 watts of power output. The module is mounted to the rear heat sink. The PA module output drive the 40 watt PA Board through connector J103. The power control circuit controls the PA module output power. The power output for the 485-505 MHz band is set for 25 watts.

PIN Diode Switch, Low Pass Filter and Directional Coupler

The output from the PA Board feeds transmit PIN diode switch D104 through J102. In transmit, switched 8 volts is applied through inductor L102, turning on PIN diodes D104 and D401. The DC path is completed through resistors R401 and R420 with the bias current set at about 40 mA. Diode D104 couples the PA Board power from J102 to low pass filter A101. Diode D401 provides an RF path to ground to protect the receiver input.

The lowpass filter reduces the harmonic output from the transmit circuit. The low pass filter feeds the directional coupler, W101 and W102. The directional coupler provides a sample of transmit power for the power control circuit. The coupler output feeds antenna jack J101.

Power Control Circuit

The Power control circuit samples the output power to the antenna to maintain a constant power level across the band. Also, a thermistor senses the heat sink temperature to reduce the power output level above 70°C. The circuit controls the supply voltage to one of the amplifier stages in PA module U101.

Directional coupler W101 and W102 provides a sample of transmit power to diode D101. Diode D101, resistor R106 and capacitor C104 produce a positive DC voltage proportional to the transmit output power level. This DC level feeds the (-) input of amplifier U103-B. Power Set potentiometer R111 and temperature sensor U105 along with buffer U104 determine the DC level to the (+) input of U103-B. Amplifier U103-B amplifiers the difference between the (-) and (+) inputs, forcing the output power level to equal the power set level by varying the drive to transistors Q102, then Q101. Transistor Q101 supplies the control voltage to PA module U101. For example, if the output power level begins to drop below the power set level, the output of U103-B increases positively, causing Q102 to conduct less. The base of Q101 rises, increasing the control voltage to the PA module, which increases the output power level back to the desired set level.

Transistor Q104, capacitor C123 and resistor R105 improve the transient stability of the power control loop when the transmit circuit is keyed.

RF is coupled from antenna jack J101 through the directional coupler and the low pass filter to PIN diode D401. In transmit, **SW 8V** is applied through inductor L102, turning on PIN diodes D104 and D401, with the DC path completed through resistors R401 and R402. Diode D401 provides an RF path to ground for the receive input while in transmit. In receive, D401 is off, allowing RF to pass by D401 unattenuated. Receive front end filtering is provided by RF filters Z401

Receive front end filtering is provided by RF filters Z401 and Z402. Both filters are fixed tuned, 3-pole, helical filters with 20 MHz bandwidths. These filters do not require tuning unless a different 20 MHz segment of the band split is required. RF amplifier transistor Q401 is a common emitter circuit with 15 dB of gain. Inductor L402 and capacitors C405 and C406 provide a broad band match from Z401 to the transistor input. Diode D402 protects the amplifier from high input signal levels. Inductor s L403 and L404 plus the associated capacitors provide a broad band impedance match from the amplifier output to RF filter Z402.

Test Point TP401 is a 50-ohm point for measuring front end gain or to align the receive circuit to another segment of the band split. The front end gain from antenna jack J101 to TP401 is typical 10 dB.

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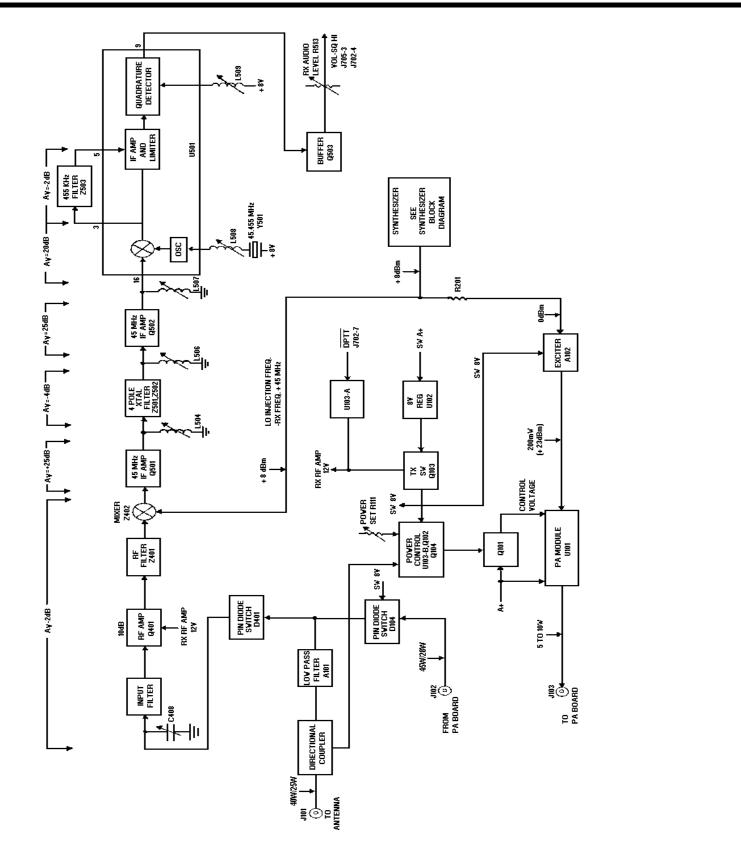
Transmit Switch

During transmit, the Audio /Logic Board microprocessor pulls the DPTT line low causing the output of amplifier U103-A to go low. Transistor Q103 turns on to supply SW 8V to the exciter module, the power control circuit and the PIN diode switch. During receive, the output of U103-A supplies 12 volts to receive circuit RF pre-amplifier transistor Q401.

RECEIVE CIRCUIT

The dual conversion receive circuit consists of a front end section, a 45 MHz first IF circuit and a 455 kHz second IF circuit with an FM detector circuit. All audio processing and squelch functions are accomplished on the Audio/Logic Board.

Front End Section



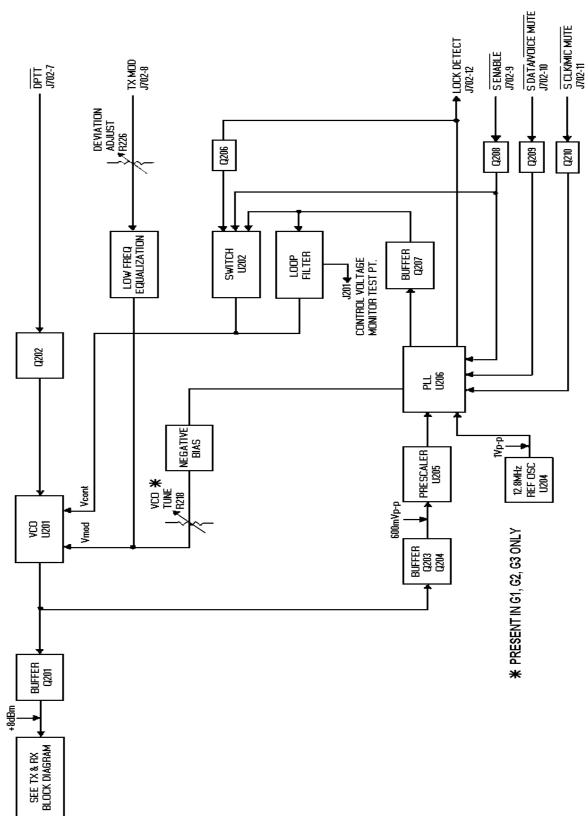


Figure 1 - TX And RX Block Diagram

Figure 2 - Frequency Synthesizer Block Diagram

Mixer Z403, is a doubly balanced diode mixer. This mixer is driven by a local oscillator signal of +10 dBm or greater to provide a good inter modulation performance, spurious performance and local oscillator isolation. The mixer conversion loss is typically 6 dB.

45 MHz IF

The first 45 MHz IF amplifier transistor Q501 is a junction FET operated in the common gate mode. This configuration offers a typical input impedance of 75 ohms. The output circuitry is turned by inductor L504 and loaded to provide the proper source termination for the four-pole crystal filter which follows.

The output of the crystal filter is matched by second IF amplifier transistor Q502. This port is also tuned by inductor L506 and loaded to provide the proper filter termination. Transistor Q502 is a dual gate FET operation at a bias current of about 10 milliamps. The output of Q502 is tuned by inductor L507 for maximum gain at 45 MHz and is loaded by the 2nd mixer in the U501 chip. This O502 stage has a relatively high input and output impedance and provides high isolation within the active device.

Converter/IF/Detector IC

The IF IC, U501, is a MC3361 chip. Pins 1 and 2 connect to an internally biased oscillator transistor. The external circuitry of this oscillator transistor includes crystal Y501 and forms an oscillator circuit operating at 45.455 MHz. The frequency of this third mode oscillator is adjusted by inductor L508. The 45 MHz IF signal is translated to 455 kHz and appears at Pin 3 of U501. This IF signal is filtered by 6-pole ceramic filter Z503 and drives the internal 455 kHz amplifier and limiter. The limited 455 kHz, in turn, drives an internal quadrature detector. The phase shift network needed by the quadrature detector is provided by inductor L509. The audio output port is Pin 9 on U501. Inductor L509 is adjusted for maximum audio output level. The audio signal at Pin 9 is filtered by resistor R512 and capacitor C519 to reduce IF feed through. Buffer amplifier Q503 drives audio potentiometer R513. This allows a VOL/SQ HI signal of which the amplitude may be set for proper system operation using R513.

Power Distribution

UN switched 13.8 Volts (A+) is supplied to the RF Board through connector J704 and feeds power control transistor Q101 and PA module U101.

Switched 13.6 Volts (A+) is supplied to the RF Board through connectors J702 and J705 and feeds regulators U102, U207 and U502. Regulator U102 supplies 8 Volts to the transmit switch, synthesizer 5 volt regulator U203 and the Audio/Logic Board through connector J702. Regulator U207 supplies 8.5 Volts to the synthesizer. Regulator U502 supplies 8 Volts to the receive circuit.

SERVICE NOTES

TRANSMIT CIRCUIT

Most transmit circuit problems can be isolated by checking the TX power gains shown in Figure 1- RX and TX Block Diagram. The PA Board may be bypassed by placing a jumper cable between J103 and J102 on the RF Board. The PA module U101 is capable of producing 10 watt output

Transmit DC Measurements

- 1. First ensure that DPTT is low when the microphone PTT is keyed low.
- 2. Check for approximately 8 Volts at L105 feeding the Exciter Module. If not present, troubleshoot the TX switch circuitry, TX Switch transistor Q103 and U103.
- 3. Check for approximately 7 Volts across resistors R401 and R402. If not present, check the PIN diodes D104 and D401 and the conduction path from R401 to Q103.
- Check for an adjustable voltage of 0 to 12 Volts on Pin 2 of PA module U101. At maximum power, with Power Set adjustment R111 fully clockwise, Pin 2 should be at 12 Volts. If not present, check the power control circuitry (U103, Q101, Q102 and Q104).
- 5. Check for 13.6 Volts on Pins 3 and 4 of PA module U101 and ensure a good mechanical and electrical ground from the PA module to the bracket and casting.

RECEIVE CIRCUIT

To isolate a receiver circuit problem refer to the Receive Circuit Symptoms and Checks chart as follows:

1.	U502 regulator.
2.	The level and frequency o
3.	The level and frequency o
4.	Quadrature detector circuit
5.	Quadrature detector coil to
1.	Consult Figure 1 - RX and troubleshoot. NOTE: Use TP401. A 50-ohm probe r or Z402 without sweep eq sharply reduced.
2.	Input cable.
3.	PIN Diode switch is short
1.	Both mixer injection frequ
2.	Quadrature detector coil to
3.	Crystal filter source and lo
4.	Z503: 455 kHz ceramic fi
	2. 3. 4. 5. 1. 2. 3. 1. 2. 3.

RECEIVE FRONT END TUNING

Each receive front end has been preset to a fixed 20 MHz segment of each split. To adjust the front end for another 20 MHz segment of the split, a sweep tuning procedure will be required to maintain the necessary bandwidth.

- 1. Apply a sweep signal generator (or tracking generator) with markers set for the desired 20 MHz bandwidth at antenna jack J101.
- 2. Measure the RF signal at TP401 with a high impedance RF probe. A 50-ohm RF probe may be used at TP401 if coupling capacitor C415 is removed (If damaged, C415 may be replaced by a short piece of hookup wire).
- 3. Connect the RF sweep detector/display (or spectrum analyzer) to the RF probe.
- 4. Tune the slugs of Z401 and Z402 for the required 20 MHz bandwidth. Ripple will be 1 dB to 2 dB typical.

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CHECKS

of the first mixer injection frequency.

of the second mixer injection frequency.

uit.

tuning.

nd TX Block Diagram for RX stage gains and a high impedance RF probe when measuring gain at may be used if C415 is removed. DO NOT adjust Z401 equipment or the 20 MHz sensitivity bandwidth will be

ted.

uencies.

tuning.

load tuning.

ilter.

Reduce the RF input level, if necessary, to keep O401 out of saturation and protection diode D402 off. The filter response will not change at lower RF input levels if the front end has been tuned up correctly.

SYNTHESIZER CIRCUIT

DC Analysis

An 8.5 Vdc is supplied by regulator U207 and serves as the biasing voltage for transistor circuits Q204, Q206, Q207, Q208, Q209 and Q210. Resistor R207 decouples the 8.3 volts for use in VCO module U201. The 10 milliamp current drain of this module results in approximately 6.5 Vdc on Pin 4. Transistor Q201 also draws approximately 25 milliamps, resulting in a collector voltage of 3.7 Vdc at the junction of resistor R204 and capacitor C201. Lack of VCO RF output will modify this voltage.

Regulator U203 uses the 8 volts from transmit regulator U102 to generate 5 volts for U204 and U205.

Wave forms

Wave forms associated with the synthesizer were measured with a 10 meg-ohm, 30 pF probe. Use DC coupling (see Figures 3-8).

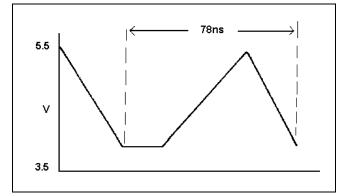


Figure 3 - REFERENCE OSCILLATOR Input To U206, Pin 2)

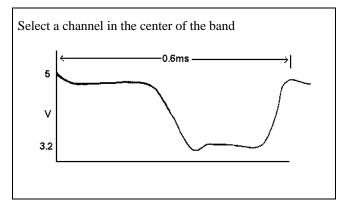


Figure 4 - Fin (Input to U206, Pin 10)

The top of the ramp is approximately 0.8 Vdc greater than the control voltage on PD out, Pin 17. A channel in the center of the band is shown.

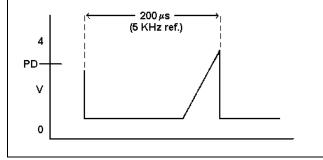


Figure 5 - RAMP (Generated in U206 and appears on Pin 15)

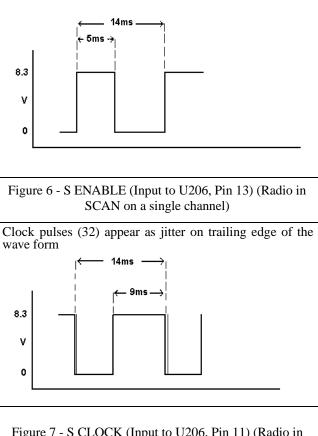


Figure 7 - S CLOCK (Input to U206, Pin 11) (Radio in SCAN on a single channel)

When expanded, data can be seen to be changing as two different bit patterns are loaded

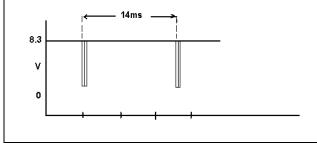


Figure 8 - S DATA (Input to U206, Pin 12) (Radio in SCAN on a single channel)

Module Isolation

Reference Oscillator U204:

Look for a wave form similar to the reference (Figure 3) on Pin 2. If wave form is not present, the oscillator module is probably defective.

VCO U201:

Connect a DC power supply to Pin 3. With 2.5 Vdc on Pin 3, the output of U201 (Pin 5) should be approximately 197 MHz. With 6.5 Vdc on Pin 3, the output should be approximately 212 MHz. These values are correct for the 440-470 MHz split, with the ranges 179-194 MHz and 212-233 MHz being correct for the lower and upper split, respectively.

Power output of the VCO can be measured by connecting a coax directly to the module, between Pin 5 and ground. The output should be approximately 0 dBm with capacitor C237 still connected in the circuit. In transmit, a negative bias should exist on Pin 1. If not present, check transistors Q202, Q203 and capacitor C206 before removing the VCO.

Prescaler U205:

Connect Pin 3 of the VCO to 4.5 Vdc. With the radio in receive, monitor the frequencies of the VCO at the connection of capacitor C210 and resistor R211. DC short Pin 1 of U205 to ground to cause divide by 129 to occur. The frequency output at Pin 3 should be the VCO frequency divided by 129. Tie Pin 1 to Pin 7 (5 volts) to cause divide 128 to occur. check Pin 3 to verify that this occurs. Improper division may indicate a defective prescaler.

Bilateral Switch U202:

The bilateral switch is used to short around parts of the loop filter during channel scan. A shorted (to ground or adjacent gate) gate may be isolated by comparing voltages through the loop filter to those of a functioning radio. Defective gates might be suspected when the radio does not change frequency quickly enough.

Phase-Lock-Loop U206:

There are no other specific checks which aid in evaluation of U206. Usually, it is suspected only if all other checks are

Transistor O201:

After checking for proper DC operation, measure the frequency and gain from the VCO, Pin 5 to R202/C203. the gain should be approximately 10 dB at 2 times the VCO frequency.

PA MODULE REPLACEMENT

To Remove PA Module U101

To Install PA Module U101

- ment module.
- 3. screws.

OK. Before changing, inspect chip components for mechanical damage and check resistance through the loop filter.

1. Unsolder the five leads from U101, using either solder removal braid, or a mechanical de-soldering tool. These leads are fragile and can be bent very easily. DO NOT unsolder the shield that wraps around the module.

2. Remove the RF Board from the radio chassis assembly. Refer to the disassembly procedure provided in the Service Section. Carefully slide the module out of the shield and away from the board.

1. Apply some silicone grease to the metal side of the replace-

2. Carefully insert the five leads from the module into the five corresponding printed wire board holes and slide the module into the shield. DO NOT solder the leads yet.

Slide the RF Board assembly back into the radio frame. Reinstall all hardware, harnesses, cables, etc. Replace all

4. Install the two PA bracket screws before soldering the four modules leads. Trim excess wire.

RF BOARD 188D5062G2 (403-440 MHz) 188D5062G1 (440-470 MHz) 188D5062G3(470-512 MHz) Issue 7

SYMBOL	PART NO.	DESCRIPTION
A102		TRANSMIT EXCITER BOARD 19C851643G1 - 403-440 MHz 19C851643G2 - 440-470 MHz 19C851643G3 - 470-512 MHz
		CAPACITORS
C1 and C2	19A702061P77	Ceramic: 470pF, $\pm 5\%,50$ VDCW, temp coef 0 \pm 3 0 PPM°C.
C3	19A702061P17	Ceramic: 12pF, \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 1).
C3	19A702061P13	Ceramic: 10pF, \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C3	19A702061P11	Ceramic: 6.8pF, $\pm 0.5 pF$, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 3).
C4	19A702061P13	Ceramic: 10pF, \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 1).
C4	19A702061P11	Ceramic: 6.8pF, $\pm 0.5 pF$, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 2 and 3).
C5	19A702061P61	Ceramic: 100pF, \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 1).
C5	19A702061P45	Ceramic: 47pF, $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Groups 2 and 3).
C6	19A702061P10	Ceramic: 5.6pF, ± 0.5 pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 1).
C6	19A702061P9	Ceramic: 4.7pF, $\pm 0.5pF$, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 2 and 3).
C7	19A702061G12	Ceramic: 8.2pF, \pm 0.5pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 1).
C7	19A702061P11	Ceramic: 6.8pF, \pm 0.5pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 2 and 3).
C8 thru C10	19A702061P77	Ceramic: 470pF, $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C.
C11	19A702052P14	Ceramic: 0.01 µF ±10%, 50 VDCW.
C12	19A702061P12	Ceramic: 8.2 pF $\pm 0.5 \text{pF}$ 50 VDCW, temp coef 0 ± 60 PPM/°C (Used in Group 1).
		DIODES
D1	19A702525P2	Silicon PIN: sim to MMBV3401.
		INDUCTORS
L1		Part of printed wire board 19C851644P1.
L2	19B800891P6	Coil: RF: 0.084 H; sim to Paul Smith SK-890-1.
L3 thru L5		Part of printed wire board 19C851644P1.
		TRANSISTORS
Q1	19A704708P2	Silicon NPN: sim to NEC2SC3356.
Q2	19A701940P1	Silicon NPN: sim to MRF-559.
		RESISTORS
R1	19B800607P471	Metal Film: 470 ohms ±5%, 1/8 Watt.
R2	19B800607P222	Metal Film: 2.2K ohms ±5%, 1/8 Watt.
R3	19B800607P102	Metal Film: 1K ohms ±5%, 1/8 Watt.
R4	19B800607P330	Metal Film: 33 ohms ±5%, 1/8 Watt.
R5	19B800607P272	Metal Film: 2.7K ohms ±5%, 1/8 Watt.
R6	19B800607P331	Metal Film: 330 ohms ±5%, 1/8 Watt.
R7	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.

SYMBOL	PART NO.	DESCRIPTION	SYMBOL	PART NO.	
R8	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	C142	19A702236P38	
		CAPACITORS	0004	404700050044	
C101	19A705108P36	Mica: 91pF ±5% 500 VDCW, temp coef 0 + 50 PPM/°C.	C201 C202	19A702052P14 19A702061P99	
C103	19A702061P19	Ceramic: 13pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).	C203	19A702061P11	
C103	19A702061P17	Ceramic: 12pF ±5%, 50 VDCW, temp coef 0 ±30PPM/°C (Used in Groups 1 and 3).	C204	19A702052P26	
C104	19A702061P99	Ceramic: 1000pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	C205	19A701534P17	
C105	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	C206	19A702052P5	
C106	19A702061P73	Ceramic: 330pF \pm 5%. 50 VDCW, temp coef 0 \pm 30 PPM/°C.	C207 C208	19A701534P8 19A702052P14	
C107	19A701534P8	Tantalum: 22μF ±20%, 16VDCW.	C210	19A702052P14	
C108	19A701534P16	Tantalum: 6.8μ F ±20%, 35 VDCW.	C211	19A702061P33	
C109	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.			
and C110	10/11/02/02/11		C212 C213	19A702052P5 19A702052P14	
C111	19A701534P16	Tantalum: 6.8μF ±20%, 35 VDCW.	and C214	1347020321 14	
C113 thru	19A702061P73	Ceramic: 330pF \pm 5%. 50 VDCW, temp coef 0 \pm 30 PPM/°C.	C215	19A700004P1	
C115		1 T W/ C.	C216	19A702052P14	
C116	19A702061P61	Ceramic:100pF \pm 5%, 50 VDCW, temp coef 0 \pm 30	C217	19A700004P11	
C116	19A702236P13	PPM°/C (Used in Groups 1 and 3). Ceramic: 3.3pF ± 0.5 pF, 50 VDCW, temp coef 0 \pm 120	C218	19A702061P29	
C117	19A702052P22	PPM/°C (Used in Group 2). Ceramic: 0.047µF ±10%, 50 VDCW.	C219	19A702061P93	
C118	19A703314P10	Electrolytic: 10µF -10 +50%, 50 VDCW; Sim to Panasonic LS Series.	C220	19A702052P14	
C119	19A702061P73	Ceramic: 330pF \pm 5%. 50 VDCW, temp coef 0 \pm 30 PPM/°C.	C222	19A702061P99	
C120	19A702236P50	Ceramic: 100pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	C223	19A702052P14	
C121	19A702052P26	Ceramic: 0.1μF ±10%, 50 VDCW.	C224	19A702061P77	
C122	19A702052P28	Ceramic: 0.022µF ±10%, 50 VDCW.	C225	19A702061P103	
C123	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	C226	19A701534P17	
C124	19A705108P36	Mica: 91pF ±5% 500 VDCW, temp coef 0 + 50	C220	19A702052P14	
C125	19A702061P73	PPM/°C. Ceramic: 330pF ±5%. 50 VDCW, temp coef 0 ± 30	C228	19A702061P9	
and C126		PPM/°C.	C229	19A702061P61	
C127	19A702061P93	Ceramic: 2200pF ±5%, 50 VDCW.	0000	404700050000	
C130	19A705108P3	Mica: 3.9pF ± 0.25 pF, 500 VDCW, temp coef 0 +200 PPM/°C (Used in G1, G3).	C230 C231	19A702052P26 19A703314P10	
C130	19A705108P1	Mica: 3.3 pF ± 0.25 pF, 500 VDCW, temp coef 0 +200 PPM/°C (Used in G2).	C232	19A702052P14	
C131	19A705108P15	Mica: 12pF ±5%, 500 VDCW, temp coef 0 +100 PPM/°C (Used in G1, G3).	C234	19A702052P14	
C131	19A705108P17	Mica: 15pF ±5%, 500 VDCW, temp coef 0 +100 PPM/°C (Used in G2).	C236 C237	19A702052P14 19A702061P17	
C132	19A705108P206	Mica: 2.2pF ±5%, 500 VDCW, temp coef 0 +100 PPM/°C (Used in G2).	C238	19A702061P9	
C132	19A705108P208	Mica: 3pF ±0.25 pF, 500 VDCW, 0 +200 PMM/°C (Used in G3).	C239	19A702061P12	
C132	19A705108P3	Mica: 3.9pF ±0.25pF, 500 VDCW, temp coef 0 +200 PPM/°C (Used in G1).	C239	19A702061P11	
C133	19A702052P26	Ceramic: 0.1μ F ±10%, 50 VDCW.			
C134	19A701534P16	Tantalum: 6.8μF ±20%, 35 VDCW.	C240	19A702061P25	
C135	19A705108P36	Mica: 91pF ±5% 500 VDCW, temp coef 0 + 50 PPM/°C.	C241	19A702061P73	
C140	19A702236P19	Ceramic: 5.6 pF \pm 0.5 pF, 50 VDCW, temp coef 0 \pm	C242	19A702052P26	
and C141		60 PPM/°C. (Used in Groups 1 and 3).	C242	19A700233P9	I
C141 C142	19A702236P28	Ceramic: 12 pF \pm 5%, 50 VDCW, temp coef 0 \pm 30	C245	19A703314P10	ļ
		PPM/°C. (Used in G1, G2).	·		

*COMPONENTS ADDED, DELECTED OR CHANGED BY PRODUCTION CHANGES

PARTS LIST

PART NO.	DESCRIPTION
404700000000	
19A702236P38	Ceramic: 33 pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C. (Used in G3).
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702061P99	Ceramic: 1000pF $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702061P11	Ceramic: 6.8 pF ± 5 pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C.
19A702052P26	Ceramic: 0.1 µF ±10%, 50 VDCW.
19A701534P17	Tantalum: 47µF ±20%, 10 VDCW.
19A702052P5	Ceramic: 1000pF ±10%, 50 VDCW.
19A701534P8	Tantalum: 22µF ±20%, 16 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702061P33	Ceramic: 27pF ±5%, 50 VCDW, temp coef 0 \pm 30 PPM/°C.
19A702052P5	Ceramic:1000pF ±10%, 50 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A700004P1	Metallized Polyester: 0.068 μF ±10%, 63 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A700004P11	Metallized Polyester: 1µF \pm 10%, 63 VDCW.
19A702061P29	Ceramic: 22pF ±5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702061P93	Ceramic: 2200pF $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702061P99	Ceramic: 1000pF $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702052P14	Ceramic: 0.01µF 10%, 50 VDCW.
19A702061P77	Ceramic: 470pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702061P103	Ceramic: 4700pF \pm 5%, 50 VDCW, temp coef \pm 30 PPM/°C at 85°C.
19A701534P17	Tantalum: 47µF ±20%, 10 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702061P9	Ceramic: 4.7pF $\pm 0.5 p$ F, 50 VDCW, temp coef 0 \pm 60 PPM/°C.
19A702061P61	Ceramic: 100pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702052P26	Ceramic: 0.1µF ±10%, 50 VDCW.
19A703314P10	Electrolytic: 10μ F -10 +50%, 50 VDCW; Sim to Panasonic LS Series.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
19A702061P17	Ceramic: 12pF $\pm 5\%,50$ VDCW, temp coef 0 ± 30 PPM/°C.
19A702061P9	Ceramic: 4.7pF $\pm 0.5p$, 50 VDCW, temp coef 0 \pm 60 PPM/°C.
19A702061P12	Ceramic: 8.2pF ± 0.5 pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 1 and 2).
19A702061P11	Ceramic: 6.8pF ± 0.5 pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 3).
19A702061P25	Ceramic: 18pF ±5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.
19A702061P73	Ceramic: 330pF $\pm 5\%$. 50 VDCW,temp coef 0 \pm 30 PPM/°C.
19A702052P26	Ceramic: 0.1µF ±10%, 50 VDCW.
	Ceramic: 2200pF ±20%. 50 VDCW.
19A700233P9	

LBI-39017H

SYMBOL	PART NO.	DESCRIPTION
C246	19A702061P73	Ceramic: 330pF \pm 5%. 50 VDCW, temp coef 0 \pm
		30 PPM/°C.
C247	19A702052P14 19A702061P73	Ceramic: 0.01μ F ±10%, 50 VDCW.
C248 and C249	19A702061P73	Ceramic: 330pF ±5%. 50 VDCW, temp coef 0 \pm 30 PPM/°C.
C250	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.
C251 and C252	19A703314P10	Electrolytic: 10μF -10 +50%, 50 VDCW; Sim to Panasonic LS Series.
C253	19A701534P4	Tantalum: 1µF ±20%, 35 VDCW.
C254	19A701534P7	Tantalum: 10μF ±20%, 16 VDCW.
C255	19A701534P4	Tantalum: 1µF ±20%, 35 VDCW.
C402	19A705108P9	Mica: 6.8pF ±0.25pF. 500 VDCW, temp coef 0 +200 PPM/°C (Used in Groups 1 and 3).
C402	19A705108P14	Mica: 11pF ±5%, 500 VDCW, temp coef 0 +200 PPM/°C (Used in Group 2).
C403	19A702236P15	Ceramic: 3.9pF $\pm 0.25 pF$ @3kHz, temp coef 0 \pm 30 PPM/°C.
C404	19A702061P63	Ceramic: 120pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C405	19A702061P13	Ceramic: 10pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C405	19A702061P11	Ceramic: 6.8pF, \pm 0.5pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 1 and 3).
C406	19A702061P13	Ceramic: 10pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C406	19A702061P10	Ceramic: 5.6pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 1).
C406	19A702061P9	Ceramic: 4.7pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 3).
C407	19A702052P26	Ceramic: 0.1µF ±10%, 50 VDCW.
C408	19A702061P99	Ceramic: 0.1µF ±10%,50 VDCW, temp coef 0 \pm 30 PPM/°C.
C409	19A702236P11	Ceramic: 2.7pF, \pm 0.25pF, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Groups 1 and 3).
C409	19A702236P10	Ceramic: 2.2pF \pm 0.25pF, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C410	19A702236P15	Ceramic: 3.9pF ±0.25pF, 50 VDCW, temp coef 0 ± 30 PPM/°C (Used in Group 1).
C410	19A702236P21	Ceramic: 6.8pF \pm 0.5pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 2).
C410	19A702236P17	Ceramic: 4.7pF $\pm 0.5 p$ F, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Group 3).
C411	19A702061P11	Ceramic: 4.7pF \pm 5pF, 50 VDCW, temp coef 0 \pm 60 PPM/°C (Used in Groups 1 and 2).
C411	19A702061P7	Ceramic: 4.7pF $\pm 0.5p$ F, 50 VDCW, temp coef 0 \pm 120 PPM/°C (Used in Group 3).
C412	19A702061P10	Ceramic: 5.6pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 1).
C412	19A702061P9	Ceramic: 4.7pF $\pm 0.5p$ F, 50 VDCW, temp coef 0 \pm 60 PPM/°C Used in Group 2).
C412	19A702061P11	Ceramic: 6.8pF $\pm 0.5 p$ F, 50 VDCW, temp coef 0 \pm 60 PPM/°C Used in Group 3).
C413	19A702061P17	Ceramic: 12pF $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Groups 1 and 3).
C413	19A702061P13	Ceramic: 10pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 2).
C414	19A702234P15	Ceramic: 3.9 pF ± 0.25 pF, 50 VDCW, temp coef 0 ± 30 PPM/°C (Used in Group 1).
C414	19A702236P17	Ceramic: 4.7 pF ± 0.5 pF, 50 VDCW, temp coef 0 ± 60 PPM/°C (Used in Group 2).
C415 and C416	19A702061P63	Ceramic: 120pF $\pm 5pF,$ 50 VDCW, temp coef 0 \pm 120 PPM/°C.
C417	19A702061P9	Ceramic: 4.7pF $\pm 0.5 p$ F, 50 VDCW, temp coef 0 \pm 60 PPM/°C.
C418	19A702052P5	Ceramic: 1000pF ±10%, 50 VDCW.

SYMBOL	PART NO.	DESCRIPTION	SYMBOL	PART NO.
C419	19A702236P15	Ceramic: 3.9pF \pm 0.25pF, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	J705	19A700072P30
C421	19A702236P52	Ceramic: 120pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Groups 1 and 2).		
C421	19A702236P50	Ceramic: 100pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 3).	L102	19A700024P7
C502	19A702061P99	Ceramic: 1000pF $\pm 5\%,$ 50 VDCW, temp coef 0 \pm 30 PPM/°C (Used in Group 3).	L103 thru	19A704921P1
C503	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	L106	
C504	19A702061P29	Ceramic: 22pF \pm 10%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	L120	19A705470P3
C505	19A702061P25	Ceramic: 18pF ±5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	L120	19A705470P8
C506	19A701534P7	Tantalum: 10μF ±20%, 16 VDCW.	L130 and	19B800891P1
C507 thru	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	L131 L202	19A705470P6
C509 C510	19A702061P6	Ceramic: 2.7pF \pm 0.5pF, 50 VDCW, temp coef 0 \pm 150 PPM/°C.	and L203	
C511	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	L202 and	19A705470P5
C512	19A702061P1	Ceramic: 1pF \pm 0.5pF, 50 VDCW, temp coef 0 \pm	L203	
		30 PPM/°C.	L401	19B800891P2
			L402	19B800891P1
C513	19A702061P12	Ceramic: 8.2pF ± 0.5 pF, 50 VDCW,temp coef 0 \pm 60 PPM/°C.	L403	19B800890P3
C514	19A702061P33	Ceramic: 27pF \pm 5%, 50 VDCW, temp coef 0 \pm 30 PPM/°C.	L404	19B800891P2
C515	19A702061P29	Ceramic: 22pF \pm 10%, 50 VDCW,temp coef 0 \pm	L405	19B800891P1
and C516		30 PPM/°C.	L502 and L503	H343CLP10022
C517 and	19A702052P26	Ceramic: 0.1µF ±10%, 50 VDCW.	L503	H343CLP10022
C518			L504	19B801413P4
C519	19A702052P5	Ceramic: 1000pF ±10%, 50 VDCW.	L505	19B209420P21
C520	19A702052P14	Ceramic: 0.01µF ±10%, 50 VDCW.	2000	100200420121
C521	19A703314P10	Electrolytic: 10µF -10 +50%, 50 VDCW; Sim to Panasonic LS Series.	L506 thru	19B801413P4
C522	19A702052P26	Ceramic: 0.1µF ±10%, 50 VDCW.	L508	19B801415P2
C523 and C524	19A701534P4	Tantalum: 1µF ±20%, 35 VDCW.	L509	19860141582
C524	19A701534P7	Tantalum: 10μF ±20%, 16 VDCW.	Q101	344A3224P1
0525			Q102	19A703197P2
		DIODES	Q103	19A704972P1
D101	19A705377P1	Silicon, Hot Carrier: simi to MMB0201.	Q104	19A700076P2
D104	344A3316P1	Silicon PIN: sim to MA4P1250.	Q105	19A700059P2
D106	19A702526P2	Silicon: Schottky Barrier;sim to Bat 17.		
D202	19A702526P2	Silicon: Schottky Barrier;sim to Bat 17.	Q201	19A704708P2
and D203		•	Q202	19A700059P2
D401	344A3316P1	Silicon PIN: sim to MA4P1250.	Q203	19A700076P2
D402	19A700155P2	Silicon, fwd Current: 100 mA, 35 PIV.	Q204	19A704708P2
D501	19A700028P1	Silicon: 75 mA, 75 PIV; sim to 1N4148.	Q206	19A700076P2
and D502			Q207	19A700059P2
		JACKS	Q208	19A700023P2
J101 thru J103	19A705512P1	RF jack.	Q209 and	19A702084P2
J201	19A700072P1	Printed wire: 2 contacts rated at 2.5 amps; sim to	Q210	19A704708P2
and J501		Molex 22-03-2021.	Q401 Q501	19A702524P2
J702	19A704779P11	Connector; sim to Molex 22-17-2122.	Q502	19A116818P3
J704	19A700072P29	Printed wire: 3 contacts rated at 2.5 amps; sim to Molex 22-03-2031.	Q503	19A700023P2

	PART NO.	DESCRIPTION
1	9A700072P30	Printed wire: 4 contacts rated at 2.5 amps; sim to
ľ		Molex 22-27-2041.
L		INDUCTORS
	9A700024P7	Coil, RF: 330nH ±5%.
1	9A704921P1	Coil.
I.	0.1705 (70.00	
1	9A705470P3	Coil, RF: 15μ H $\pm 20\%$, sim to Toko 380NB-15nH (Used in Groups 1 and 3).
1	9A705470P8	Coil, RF: 39µH ±20%, sim to Toko 380NB-39nH (Used in Group 2).
1	9B800891P1	Coil, RF choke: sim to Paul Smith SK-890-1.
1	9A705470P6	Coil: 27nH; sim to Toko 380NB-27nH (Used in Groups 1 and 2).
1	9A705470P5	Coil: 22nH; sim to Toko 380NB-22nH (Used in Group 3).
1	9B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.
1	9B800891P1	Coil, RF Choke: sim to Paul Smith SK-890-1.
1	9B800890P3	Coil, RF: 11.7 μ H ±5%, sim to Paul Smith
1	9B800891P2	SK-896-1. Coil, RF Choke: sim to Paul Smith SK-890-1.
	9B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.
	H343CLP10022	Coil,Fixed: 10μH ±10%. (G2, G3).
ľ		
F	H343CLP10022	Coil,Fixed: 10μH ±10%. (G1).
	9B801413P4	Coil:39MHz.
	9B209420P21	Coil, RF:.4.7 μ H ±5%, 1.20 ohms DC res max;
1	9B801413P4	sim to Jeffers 4436-8J. Coil, 39MHz.
1	9B801415P2	Transformer:455 KHz; sim to AEPD 162B3277P17.
		TRANSISTORS
3	344A3224P1	Silicon, NPN: sim to Motorola MJP3055.
1	9A703197P2	Silicon, PNP: sim to MMBT4403 Low profile Pkg.
1	9A704972P1	Silicon, PNP: sim to Motorola 2N4918.
1	9A700076P2	Silicon, PNP: sim to MMBT3904 Low profile Pkg.
1	9A700059P2	Silicon PNP: sim to MMBT 3906 Low Profile Pkg. (Used in Groups 1 and 3).
1	9A704708P2	Silicon, NPN: sim to NEC 2SC3356.
1	9A700059P2	Silicon, PNP: sim to MMBT3906 Low profile Pkg.
1	9A700076P2	Silicon, PNP: sim to MMBT3904 Low profile Pkg.
1	9A704708P2	Silicon, NPN: sim to NEC 2SC3356.
1	9A700076P2	Silicon, PNP: sim to MMBT3904 Low profile Pkg.
1	9A700059P2	Silicon, PNP: sim to MMBT3906 Low profile Pkg.
1	9A700023P2	Silicon, NPN: sim to 2N3904.
1	9A702084P2	Silicon, NPN: sim to MPS 2369.
I		
	9A704708P2	Silicon, NPN: sim to NEC 2SC3356.
	9A702524P2	N-Type, Field Effect; sim to MMBFU310.
	9A116818P3	N-Channel, Field Effect; sim to Type 3N1877.
1	9A700023P2	Silicon, NPN: sim to 2N3904.

PARTS LIST

SYMBOL	PART NO.	DESCRIPTION	SYMBOL
			OTMEDOL
		RESISTORS	R219
R101	19B800607P103	Metal Film: 10K ohms ±5%, 1/8 Watt.	R221
R102	19B800607P510	Metal Film: 51 ohms ±5%, 1/8 Watt. (Used in Group 2).	R222
R102	19B800607P560	Metal Film: 56 ohms ±5%, 1/8 Watt. (Used in Groups	R223
		1 and 3).	R224
R103	19B800607P821	Metal Film: 820 ohms ±5%, 1/8 Watt.	R226
R104	19B800607P223	Metal Film: 22K ohms ±5%, 1/8 Watt.	R227
R105	19B800607P473	Metal Film: 47K ohms ±5%, 1/8 Watt.	R228
R106	19B800607P102	Metal Film: 1K ohms ±5%, 1/8 Watt.	R229
R107	19B800607P394	Metal Film: 390K ohms ±5%, 1/8 Watt.	R230
R108	19B800607P123	Metal Film: 12K ohms ±5%, 1/8 Watt.	R231
R109	19B800607P394	Metal Film: 390K ohms ±5%, 1/8 Watt.	R232
R110	H212CRP210C	Metal Film: 1K ohms ±5%, 1/8 Watt.	R233
R111	19B800779P8	Variable: 4.7K ohms ±25%, 100 VDCW, 0.3 Watt.	R234
R112	19B800607P103	Metal Film: 10K ohms ±5%, 1/8 Watt.	R235
R113	19B800607P102	Metal Film: 1K ohms ±5%, 1/8 Watt.	R236
R114	19B800607P103	Metal Film: 10K ohms ±5%, 1/8 Watt.	R237
R115	19B800607P562	Metal Film: 5.6K ohms ±5%, 1/8 Watt.	R238
R116	19B800607P183	Metal Film: 18K ohms ±5%, 1/8 Watt.	R239
R117	19B800607P221	Metal Film: 220 ohms ±5%, 1/8 Watt.	R240
R118	19A702931P326	Metal Film: 18.2K ohms ±5%, 1/8 Watt.	R241
R119	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	R242
R120	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	R245
R121	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	R246
R122	19B800607P821	Metal Film: 820 ohms ±5%, 1/8 Watt.	R248
R123	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	R249
R124	19B800607P471	Metal Film: 470 ohms ±5%, 1/8 Watt.	R251
R125	19A702931P259	Metal Film: 4020 ohms ±5%, 1/8 Watt.	thru R254
R126	19A702931P201	Metal Film: 1000 ohms ±5%, 1/8 Watt.	R255
R127	19A702931P262	Metal Film: 4320 ohms ±5%, 1/8 Watt.	R256
R128	19B800607P1	Metal Film: 0 ohms ±5%, 1/8 Watt.	R401
R129	19B800607P153	Metal Film: 15K ohms ±5%, 1/8 Watt.	R403
R130	19B801251P394	Metal Film: 390K ohms ±5%, 1/8 Watt. (Used in G1,	R403
		G3).	R405
R140	19A702931P301	Metal Film: 10K ohms ±1%, 1/8 Watt.	R405
R141	19A702931P210	Metal Film: 1.24K ohms ±1%, 1/8 Watt.	R406
R142	19B800607P221	Metal Film: 220 ohms ±5%, 1/8 Watt.	
R202	19B800607P100	Metal Film: 10 ohms ±5%, 1/8 Watt.	R406
R203	19B800607P560	Metal Film: 56 ohms ±5%, 1/8 Watt.	R501
R204	19B800607P221	Metal Film: 220 ohms ±5%, 1/8 Watt.	R501
R205	19B800607P332	Metal Film: 3.3K ohms ±5%, 1/8 Watt.	R502
*R206	19B800607P222	Metal Film: 2.2K ohms ±5%, 1/8 Watt.	R503
R207	19B800607P181	Metal Film: 180 ohms ±5%, 1/8 Watt.	R504
R208	19B800607P473	Metal Film: 47K ohms ±5%, 1/8 Watt.	R505
R209	19B800607P332	Metal Film: 3.3K ohms ±5%, 1/8 Watt.	R506
R210	19B800607P332	Metal Film: 3.3K ohms ±5%, 1/8 Watt.	R507
R211	19B800607P101	Metal Film: 100 ohms ±5%, 1/8 Watt.	R508
R213	19B800607P103	Metal Film: 10K ohms ±5%, 1/8 Watt.	R509
R214	19B800607P331	Metal Film: 330 ohms \pm 5%, 1/8 Watt.	R510
R215	19B800607P822	Metal Film: 8.2K ohms ±5%, 1/8 Watt.	R511
R216	19B800607P222	Metal Film: 2.2K ohms ±5%, 1/8 Watt.	R512
R217	19B800607P101	Metal Film: 100 ohms ±5%, 1/8 Watt.	R513
R218	19B800779P16	Variable: 100K ohms ±25%, 100 VDCW, 0.3 Watt.	R514
	-		R515

PART NO.

9B800607P273 19B800607P154 19B800607P333 19B800607P105 19B800607P102 I9B800779P4 19B800607P473 19B800607P223 I9B800607P183 19B800607P332 9B800607P472 19B800607P103 19B800607P332 I9B800607P472 19B800607P183 I9B800607P471 I9B800607P103 9B800607P103 19B800607P103 19B800607P154 I9B800607P154 19B800607P154 9B800607P223 19B800607P102 19B800607P1 19B800607P100 I9B800607P100

19B800779P16 19B800607P103 19B801486P151 19B800607P102 9B800607P472 9B800607P271 I9B800607P391 19B800607P271 I9B800607P471 I9B800607P271 I9B800607P181 9B800607P270 9B800607P562 I9B800607P270 I9B800607P683 9B800607P823 19B800607P183 I9B800607P101 19B800607P272 19B800607P270 9B800607P473 19B800607P822 I9B800779P4 9B800607P103 19B800607P821

DESCRIPTION

Metal Film: 27K ohms ±5%, 1/8 Watt. Metal Film: 150K ohms ±5%, 1/8 Watt. Metal Film: 33K ohms ±5%, 1/8 Watt. Metal Film: 1M ohms ±5%, 1/8 Watt. Metal Film: 1K ohms ±5%, 1/8 Watt. Variable: 1k ohms ±25%, 100 VDCW, 0.3 Watt. Metal Film: 47K ohms ±5%, 1/8 Watt. Vetal Film: 22K ohms ±5%, 1/8 Watt. Metal Film: 18K ohms ±5%, 1/8 Watt. Metal Film: 3.3K ohms ±5%, 1/8 Watt. Metal Film: 4.7K ohms ±5%, 1/8 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 3.3K ohms ±5%, 1/8 Watt. Metal Film: 4.7K ohms ±5%, 1/8 Watt. Metal Film: 18K ohms ±5%, 1/8 Watt. Metal Film: 470 ohms ±5%, 1/8 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 150K ohms ±5%, 1/8 Watt. Metal Film: 150K ohms ±5%, 1/8 Watt. Metal Film: 150K ohms ±5%, 1/8 Watt. Metal Film: 22K ohms ±5%, 1/8 Watt. Metal Film: 1K ohms ±5%, 1/8 Watt. Metal Film: jumper. Metal Film: 10 ohms ±5%, 1/8 Watt.

Metal Film: 10 ohms ±5%, 1/8 Watt.

Variable: 100K ohms ±25%, 100 VDCW, 0.3 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 150 ohms ±5%, 1/2 Watt. Metal Film: 1K ohms ±5%, 1/8 Watt. Metal Film: 4.7K ohms ±5%, 1/8 Watt. Metal Film: 270 ohms ±5%, 1/8 Watt, Metal Film: 390 ohms ±5%, 1/8 Watt. (G1). Metal Film: 270 ohms ±5%, 1/8 Watt. (G2). Metal Film: 470 ohms ±5%, 1/8 Watt. (G3). Metal Film: 270 ohms ±5%, 1/8 Watt. (G1, G2). Metal Film: 180 ohms ±5%, 1/8 Watt. (G3). Metal Film: 27 ohms ±5%, 1/8 Watt. Metal Film: 5.6K ohms ±5%, 1/8 Watt. Metal Film: 27 ohms ±5%, 1/8 Watt. Metal Film: 68K ohms ±5%, 1/8 Watt. Metal Film: 82K ohms ±5%, 1/8 Watt. Metal Film: 18K ohms ±5%, 1/8 Watt. Metal Film: 100 ohms ±5%, 1/8 Watt. Metal Film: 2.7K ohms ±5%, 1/8 Watt. Metal Film: 27 ohms ±5%, 1/8 Watt. Metal Film: 47K ohms ±5%, 1/8 Watt. Metal Film: 8.2K ohms ±5%, 1/8 Watt. variable: 1K ohms ±25%. 100 VDCW, 0.3 Watt. Metal Film: 10K ohms ±5%, 1/8 Watt. Metal Film: 820 ohms ±5%, 1/8 Watt.

PARTS LIST

SYMBOL	PART NO.	DESCRIPTION
		INTEGRATED CIRCUITS
U101	19A705457P1	RF Power Amplifier Module. Part of next highter assembly (Used in Group 2).
U101	19A705457P2	RF Power Amplifier Module. Part of next highter assembly (Used in Group 1).
U101	19A705457P3	RF Power Amplifier Module. Part of next highter assembly (Used in Group 3).
U102	RYT1246003/4	IC; sim to LM35.
U103	19A701789P2	Linear: Dual Op Ampl.; sim to MM358.
and U104		
U105	RYT1246003/4	IC LM35.
U201	19D901958G4	Voltage Controlled Oscillator (Used in Group 1).
U201	19D901958G3	Voltage Controlled Oscillator (Used in Group 2).
U201	19D901958G5	Voltage Controlled Oscillator (Used in Group 3).
U202	19A700029P44	Digital: Bilateral Switch.
U203	19A704971P1	Linear: 5-Volt Regulator; sim to MC78L05ACP.
U204	19B801351P27	Crystal Oscillator, temperature compensated.
U205	19A704287P2	Prescaler: 128, 129; sim to MC12018.
U206	19B800902P4	Digital: Synthesizer, CMOS Serial Input.
U207	344A3820P1	8-Volt Regulator.
U501	19A704619P1	Linear: Osc/Mixer/IF/Det/Ampl; sim to MC3361AP.
U502	19A704073P2	Linear: 8-Volt Regulator; sim to MC78L08CP.
U503	344A3820P1	8-Volt Regulator.
		CRYSTALS
Y501	19A705376P5	Crystal, Fixed Frequency: 45.455 MHz \pm 10 PPM.
		FILTERS
Z401 and Z402	19A705458P4	Helical, UHF: 403-450 MHz. (Used in Group 2).
Z401 and Z402	19A705458P1	Helical, UHF: 450-470 MHz. (Used in Group 1).
Z401 and Z402	19A705458P2	Helical, UHF: 470-492 MHz. (Used in Group 3).
Z402	19B801025P1	Balanced Mixer (Double); sim to Mini-Circuits SEL-1.
Z501	19A705613G6	Monolithic Crystal: 45.000 MHz; sim to Toyocom
and Z502		45E2B2.
Z502 Z503	19B801021P2	Bandpass filter: 455 kHz ±1.5 kHz; sim to Murata CFW-455E.
		MISCELLANEOUS
	350A1232P1	CLIP.
	19B801566P1	SHIELD.
	19B801566P2	SHIELD.
13	19B801566P17	SHIELD.
14	19B801578P1	SHIELD. Used with Q502.
	PROF	DUCTION CHANGES

PRODUCTION CHANGES

Changes in the equipment to improve or to simplify circuits are identified by a "Re-vision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions. REV. A - <u>RF BOARD 188D5062G1</u> Incorporated in initial shipments. REV. B - RF BOARD 188D5062G1 To improve radio performance at temperature extremes. Changed C108, C111 & C134 (19A703314P10) to tantalum 6.8uF. C103 was 12pF (19A702061P17). R202 was 33 ohm (19B801607P330).

	PRO	DUCTION CHANGES - Cont.
REV. A - <u>R</u>	RF BOARD 188D5	
	F BOARD 188D50	
	o update parts list F BOARD 188D50	
	F BOARD 188D50	
		ance of radio and prevent shorts on PWB. New
-	WB.	0000
	<u>F BOARD 188D5</u> F BOARD 188D50	
	F BOARD 188D50	
		atness across the bandsplits.
		C131, C132, C142, R202, R206, R124, anged. C143, C144 and R130 added.
	- RF BOARD 188	.
In	corporated in initia	al shipments.
	F BOARD 188D5	
	<u>F BOARD 188D50</u> F BOARD 188D50	
		zer kick and eliminate transmitter oscillations,
		eted. R224 was changed from 4.7K ohms
	19B800607P102). F BOARD 188D50	In Group 2 resistor R130 was deleted. 062G1
	F BOARD 188D50	
		odulation, moved C207 from component side to
	F BOARD 188D50	I (- to C208 and + to ground).
	F BOARD 188D50	
Т	o improve receiver	spurious response due to 2nd IF image, R501 was
	30 ohme (19R2004	607P181) and deleted L502 (H343CLP10022). older side of board. New shields added to Q502
L		
a		
REV. E - <u>R</u>	503 relocated to so nd to solder side o F BOARD 188D50	if board.)62G4
REV. E - <u>R</u>	503 relocated to so nd to solder side o F BOARD 188D50	f board.
REV. E - <u>R</u>	503 relocated to so nd to solder side o F BOARD 188D50	if board.)62G4
REV. E - <u>R</u>	503 relocated to so nd to solder side o F BOARD 188D50	f board.) <u>62G4</u> izer loop stability, R221 was 150K (19B800607P154).
REV. E - <u>R</u>	503 relocated to send to solder side of F BOARD 188D5(o improve synthes)	if board.)62G4
REV. E - <u>R</u>	503 relocated to send to solder side of F BOARD 188D5(o improve synthes)	if board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD
REV. E - <u>R</u>	503 relocated to send to solder side of F BOARD 188D5(o improve synthes)	of board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz)
REV. E - <u>R</u> I To	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 188D5062G4 (485-505 MHz) Issue 3
REV. E - <u>R</u> I To	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION
REV. E - <u>R</u> I To	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD
REV. E - RI	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES
REV. E - RI	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. D62G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3
REV. E - RI	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	of board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD
SYMBOL A102	503 relocated to so nd to solder side o F BOARD 188D50 o improve synthes 18	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3 CAPACITORS Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0
SYMBOL A102	503 relocated to so nd to solder side of F BOARD 188D50 o improve synthes PART NO.	of board. DE2G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION
REV. E - R To SYMBOL A102 C1 and C2	503 relocated to send to solder side of E BOARD 188D50 of improve synthes	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). 188D5062G4 (485-505 MHz) 18sue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3
REV. E - R To SYMBOL A102 C1 and C2 C3 and	503 relocated to so nd to solder side of F BOARD 188D50 o improve synthes PART NO.	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3 CAPACITORS Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0
REV. E - R To SYMBOL A102 C1 and C2 C3	503 relocated to send to solder side of E BOARD 188D50 of improve synthes	ff board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION
REV. E - R To SYMBOL A102 C1 and C2 C3 and	503 relocated to send to solder side of E BOARD 188D50 of improve synthes	f board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3 CAPACITORS Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM. Ceramic: 68 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 47 pF + or -5%, 50 VDCW, temp coef 0 +
REV. E - R To SYMBOL A102 C1 and C2 C3 and	503 relocated to send to solder side of F BOARD 188D50 p improve synthes 18 PART NO. 19A702061P77 19A702061P11	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION
REV. E - R To SYMBOL A102 C1 and C2 C3 and	503 relocated to send to solder side of F BOARD 188D50 p improve synthes 18 PART NO. 19A702061P77 19A702061P11	ff board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3
REV. E - R To SYMBOL A102 C1 and C2 C3 and C4 C6	503 relocated to send to solder side of E BOARD 188D50 o improve synthesis PART NO. 19A702061P77 19A702061P11 19A702061P45 19A702061P9	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3 CAPACITORS Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM. Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 4.7 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.
REV. E - R To SYMBOL A102 C1 and C2 C3 and C4	503 relocated to send to solder side of EBOARD 188D50 of improve synthes 18 PART NO. 19A702061P77 19A702061P11 19A702061P45	ff board. 262G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3
REV. E - R T SYMBOL A102 C1 and C2 C3 and C4 C6 C6 C7	503 relocated to send to solder side of E BOARD 188D50 o improve synthesis PART NO. 19A702061P77 19A702061P11 19A702061P45 19A702061P9 19A702061P11	f board. 162G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD 88D5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3 CAPACITORS Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM. Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 4.7 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.
REV. E - R To SYMBOL A102 C1 and C2 C3 and C4 C6 C6 C7 C8 thru	503 relocated to send to solder side of E BOARD 188D50 o improve synthesis PART NO. 19A702061P77 19A702061P11 19A702061P45 19A702061P9	f board. DE2G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD SBD5062G4 (485-505 MHz) Issue 3 DESCRIPTION TRANSMIT EXCITER BOARD 19C851643G3 TRANSMIT EXCITER BOARD 19C851643G3 Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM. Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 47 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM. Ceramic: 47 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 47 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM. Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp
REV. E - R To SYMBOL A102 C1 and C2 C3 and C4 C6 C7 C6 C7 C8	503 relocated to send to solder side of E BOARD 188D50 o improve synthesis PART NO. 19A702061P77 19A702061P11 19A702061P45 19A702061P9 19A702061P11	f board. DE2G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD SBD5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3
REV. E - R To SYMBOL A102 C1 and C2 C3 and C4 C6 C6 C7 C8 thru	503 relocated to send to solder side of E BOARD 188D50 o improve synthesis PART NO. 19A702061P77 19A702061P11 19A702061P45 19A702061P9 19A702061P11	f board. DE2G4 izer loop stability, R221 was 150K (19B800607P154). RF BOARD SBD5062G4 (485-505 MHz) Issue 3 DESCRIPTION ASSEMBLIES TRANSMIT EXCITER BOARD 19C851643G3

----- DIODES -----

19A702525P2 Silicon, PIN: sim to MMBV3401.

D1

SYMBOL	PART NO.	DESCRIPTION			
		······ INDUCTORS ······			
L1		Part of PWB.			
L2	19B800891P6	Coil, RF: .084 uH; sim to Paul Smith SK-890-1.			
L3 thru L5		Part of PWB.			
		TRANSISTORS			
Q1	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.			
Q2	19A701940P1	Silicon, NPN: sim to MRF-559.			
		····· RESISTORS ·····			
R1	19B800607P471	Metal film: 470 ohms + or -5%, 1/8 w.			
R2	19B800607P222	Metal film: 2.2K ohms + or -5%, 1/8 w.			
R3	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.			
R4	19B800607P330	Metal film: 33 ohms + or -5%, 1/8 w.			
R5	19B800607P272	Metal film: 2.7K ohms + or -5%, 1/8 w.			
R6	19B800607P331	Metal film: 330 ohms + or -5%, 1/8 w.			
R7 and R8	19B800607P100	Metal film: 10 ohms + or -5%, 1/8 w.			
		CAPACITORS			
C101	19A705108P36	Capacitor, Mica Chip: 91pF + or - 5%, 500 VDCW, temp coef 0			
C103	19A702061P17	Ceramic: 12 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.			
C104	19A702061P99	Ceramic: 1000 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/C.			
C105	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.			
C106	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.			
C107	19A701534P8	Tantalum: 22 uF + or -20%, 16 VDCW.			
C108	19A701534P16	Tantalum: 6.8 uF + or -20%, 35 VDCW.			
C109 and C110	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.			
C111	19A701534P16	Tantalum: 6.8 uF + or -20%, 35 VDCW.			
C112	19A702236P25	Ceramic: 10 pF + or5 pF, 50 VDCW, temp coef -30 PPM/'C.			
C113 thru C115	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/C.			
C116	19A702061P61	Ceramic: 100 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.			
C117	19A702052P22	Ceramic: 0.047 uF + or - 10%, 50 VDCW.			
C118	19A701534P7	Tantalum: 10 uF + or -20%, 16 VDCW.			
C119	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.			
C120	19A702236P50	Ceramic: 100 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.			
C121	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW			
C122	19A702052P28	Ceramic: 0.022 uF + or -10%, 50 VDCW.			
C123	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.			

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SYMBOL	PART NO.	DESCRIPTION					
C124	19A705108P36	Capacitor, Mica Chip: 91pF + or - 5%, 500 VDCW, temp coef 0					
C125 and	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/C.					
C126 C130	19A705108P3	Mica: 3.9pF ±0.25pF. 500 VDCW, temp coef 0 ± 200					
0130	19A703100F3	PPM/°C.					
C131	19A705108P15	Mica: 12 pF + or -5%, 500 VDCW.					
C132	19A705108P208	Mica: 3.0pF \pm 0.25pF. 500 VDCW, temp coef 0 \pm 200 PPM/°C.					
C133	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW					
C134	19A701534P16	Tantalum: 6.8 uF + or -20%, 35 VDCW.					
C140 and C141	19A702236P19	Ceramic: 5.6 pF + or5 pF, 50 VDCW, temp coef -30 PPM/'C.					
C142	19A702236P38	Ceramic: 33 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.					
C201	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C203	19A702061P11	Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.					
C204	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW					
C205	19A701534P17	Tantalum: 47 uF + or -20%, 10 VDCW.					
C207	19A701534P8	Tantalum: 22 uF + or -20%, 16 VDCW.					
C208	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C209	19A702061P93	Ceramic: 2200 pF + or - 5%, 50 VDCW, temp coef - 30 PPM.					
C210	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C211	19A702061P33	Ceramic: 27 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.					
C212	19A702052P5	Ceramic: 1000 pF + or -10%, 50 VDCW.					
C213 and C214	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C215	19A703902P3	Metal: 0.047 uF + or -10%, 50 VDCW.					
C216	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C217	19A703902P4	Metal: 0.56 uF + or -10%, 50 VDCW. (Used in G4).					
C218	19A702061P29	Ceramic: 22 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.					
C220	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C221	19A702061P93	Ceramic: 2200 pF + or - 5%, 50 VDCW, temp coef - 30 PPM.					
C222	19A702061P99	Ceramic: 1000 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/C.					
C223	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C224	19A702061P77	Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.					
C225	19A702061P103	Ceramic: 4700 pF + or - 5%, 50 VDCW, temp coef 0 + or -30 PPM/C.					
C227	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.					
C228	19A702061P13	Ceramic: 10 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.					
C229	19A702061P61	Ceramic: 100 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.					

SYMBOL	PART NO.	DESCRIPTION	SYMBOL	PART NO.	DESCRIPTION
C230	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW	C413	19A702061P17	Ceramic: 12 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.
C231	19A703314P10	Electrolytic: 10 uF -10+50%, 50 VDCW; sim to Panasonic LS Series.	C414	19A702236P21	Ceramic: 6.8 pF + or -0.5 pF, 50 VDCW, temp or -60 PPM.
C232	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.	C415	19A702061P63	Ceramic: 120 pF + or -5%, 50 VDCW, temp coef 0
C233	19A702061P77	Ceramic: 470 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.	and C416		+ or -30 PPM.
C234	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.	C417	19A702236P15	Ceramic: 3.9 pF + or25 pF, 50 VDCW, temp or -30 PPM/'C.
C236	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.	C419	19A702236P15	Ceramic: 3.9 pF + or25 pF, 50 VDCW, temp or -30 PPM/'C.
2237	19A702061P17	Ceramic: 12 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.	C421	19A702236P50	Ceramic: 100 pF + or -5%, 50 VDCW, temp coef 0
238	19A702061P9	Ceramic: 4.7 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.	C502	19A702236P52	+ or -30 PPM/C.
2239	19A702061P11	Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp			Ceramic: 120 pF, + or -5%, 50 VDCW.
		or - 60 PPM.	C503	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.
240	19A702061P25	Ceramic: 18 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.	C504	19A702061P29	Ceramic: 22 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.
C241	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.	C505	19A702061P25	Ceramic: 18 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/ ⁻ C.
C242	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW	C506	19A701534P7	Tantalum: 10 uF + or -20%, 16 VDCW.
C245	19A703314P10	Electrolytic: 10 uF -10+50%, 50 VDCW; sim to Panasonic LS Series.	C507 thru C509	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.
C246	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/C.	C510	19A702061P6	Ceramic: 2.7 pF + or - 0.5 pF, 50 VDCW, temp or - 120 PPM.
C247	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.	C512	19A702061P1	Ceramic: 1 pF + or -0.5 pF, 50 VDCW.
2248 and 2249	19A702061P73	Ceramic: 330 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.	C513	19A702061P12	Ceramic: 8.2 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.
250	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.	C514	19A702061P33	Ceramic: 27 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM/'C.
251 nd 252	19A703314P10	Electrolytic: 10 uF -10+50%, 50 VDCW; sim to Panasonic LS Series.	C515 and	19A702061P29	Ceramic: 22 pF + or - 5%, 50 VDCW, temp coef 0 + or - 30 PPM.
C253	19A701534P4	Tantalum: 1 uF + or - 20%, 35 VDCW.	C516 C517	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW
C254	19A701534P7	Tantalum: 10 uF + or -20%, 16 VDCW.	and C518	19A7 02032F 20	
C255	19A701534P4	Tantalum: 1 uF + or - 20%, 35 VDCW.	C519	19A702052P5	Ceramic: 1000 pF + or -10%, 50 VDCW.
C256	19A700233P9	Ceramic: 2200 pF + or -20%, 50 VDCW.	C520	19A702052P14	Ceramic: 0.01 uF + or - 10%, 50 VDCW.
C402	19A705108P9	Mica: 6.8 pF + or25 pF, 500 VDCW.	C521	19A703314P10	Electrolytic: 10 uF -10+50%, 50 VDCW; sim to
C403	19A702236P15	Ceramic: 3.9 pF + or25 pF, 50 VDCW, temp or -30 PPM/C.			Panasonic LS Series.
C404	19A702061P63	Ceramic: 120 pF + or -5%, 50 VDCW, temp coef 0	C522	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW
0404	19A702001F03	+ or -30 PPM.	C523 and	19A701534P4	Tantalum: 1 uF + or - 20%, 35 VDCW.
C405	19A702061P11	Ceramic: 6.8 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.	C524	10170150107	
2406	19A702061P9	Ceramic: 4.7 pF + or - 0.5 pF, 50 VDCW, temp or - 60 PPM.	C525 C526	19A701534P7 19A702236P1	Tantalum: 10 uF + or -20%, 16 VDCW. Ceramic: 0.5 pF + orI pF, 50 VDCW, temp coef
407	19A702052P26	Ceramic: 0.1uF + or - 10%, 50 VDCW			-30 PPM.
C408	19A702061P99	Ceramic: 1000 pF + or -5%, 50 VDCW, temp coef 0			DIODES
2400	404700000044	+ or -30 PPM/'C.	D101	19A705377P1	Silicon, Hot Carrier: sim to MMB0201.
2409	19A702236P11	Ceramic: 2.7 pF + or -0.25 pF, 50 VDCW, temp or -30 PPM.	D104	344A3316P1	Silicon, Pin.
C410	19A702236P17	Ceramic: 4.7 pF + or -5%, 50 VDCW, temp coef 0 + or -30 PPM.	D106	19A702526P2	Silicon: Schottky Barrier; sim to BAT 17.
2411	19A702061P7	Ceramic: 3.3 pF + or - 0.5 pF, 50 VDCW, temp or - 120 PPM.	D202 and D203	19A702526P2	Silicon: Schottky Barrier; sim to BAT 17.
C412	19A702236P11	Ceramic: 2.7 pF + or -0.25 pF, 50 VDCW, temp or -30 PPM.	D401	344A3316P1	Silicon, Pin.
			D402	19A700155P2	Silicon: 100 mA, 35 PIV; sim to BAT 18.

PARTS LIST

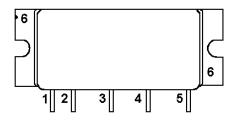
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SYMBOL	PART NO.	DESCRIPTION	SYMBOL	PART NO.	DESCRIPTION
D501 and	19A700028P1	Silicon: 75 mA, 75 PIV; sim to 1N4148.	Q202	19A700059P2	Silicon, PNP: sim to MMBT3906, low profile.
D502			Q203	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
		JACKS	Q204	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
J101 thru	19A705512P1	Connector, RF SMB Series: sim to AMP No. 221111-1.	Q206	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
J103			Q207	19A700059P2	Silicon, PNP: sim to MMBT3906, low profile.
J201	19A700072P1	Printed wire: 2 contacts rated @ 2.5 amps; sim to Molex 22-03-2021.	Q208 thru Q210	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.
J501	19A700072P1	Printed wire: 2 contacts rated @ 2.5 amps; sim to Molex 22-03-2021.	Q401	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.
J702	19A704779P11	Connector; sim to Molex 22-17-2122.	Q501	19A702524P2	N-Type, field effect; sim to MMBFU310.
J704	19A700072P29	Printed wire: 3 contacts rated at 2.5 amps; sim to Molex 22-27-2031.	Q502	19A116818P3	N Channel, field effect; sim to Type 3N1877.
J705	19A700072P30	Printed wire: 4 contacts rated at 2.5 amps; sim to Molex 22-27-2041.	Q503	19A700023P2	Silicon, NPN: sim to 2N3904.
		INDUCTORS	R101	19B800607P103	
L102	19A700024P7	Coil, RF: 330 nH + or - 10%.			Metal film: 10K ohms + or -5%, 1/8 w.
L103	19A704921P1	Coil.	R102	19B800607P560	Metal film: 56 ohms + or -5%, 1/8 w.
thru L106			R103	19B800607P821	Metal film: 820 ohms + or -5%, 1/8 w.
L120	19A705470P3	Coil, Fixed: 15 nH; sim to Toko 380NB-15nM.	R104	19B800607P223	Metal film: 22K ohms + or -5%, 1/8 w.
L130	19B800891P1	Coil, RF Choke: sim to Paul Smith SK-890-1.	R105	19B800607P473	Metal film: 47K ohms + or -5%, 1/8 w.
and L131			R106	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.
L202	19A705470P5	Coil, Fixed: 22 nH; sim to Toko 380NB-22nM.	R107	19B800607P394	Metal film: 390K ohms + or -5%, 1/8 w.
and L203			R108	19B800607P123	Metal flim: 12K ohms + or -5%, 1/8 w.
L401	19B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.	R109	19B800607P394	Metal film: 390K ohms + or -5%, 1/8 w.
L402	19B800891P1	Coil, RF Choke: sim to Paul Smith SK-890-1.	R110	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.
L403	19B800890P3	Coil, RF: 11.7 uH + or -5%, sim to Paul Smith	R111	19B800779P8	Variable, cermet: 4.7K ohms + or -25%, .3 w.
		SK-896-1.	R112	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.
L404	19B800891P2	Coil, RF Choke: sim to Paul Smith SK-890-1.	R113	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.
L405	19B800891P1	Coil, RF Choke: sim to Paul Smith SK-890-1.	R114	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.
L502	19A705470P35	Coil, Fixed: 6.8uH; sim to Toko 380LB-6R8M.	R115	19B800607P562	Metal film: 5.6K ohms + or -5%, 1/8 w.
L503	H343CLP10022	Coil, Fixed: 10 uH + or - 10%.	R116	19B800607P183	Metal film: 18K ohms + or -5%, 1/8 w.
L504	19B801413P4	Coil, 39 MHz.	R117	19B800607P221	Metal film: 220 ohms + or -5%, 1/8 w.
L505	19B209420P21	Coil, RF: 4.7 uH + or - 5%, 1.20 ohms DC res Jeffers 4436-8J.	R118	19A702931P326	Metal film: 18.2K ohms + or -1%, 200 VDCW, 1/8 w.
L506 thru L508	19B801413P4	Coil, 39 MHz.	R119 thru R121	19B800607P100	Metal film: 10 ohms + or -5%, 1/8 w.
L509	19B801415P2	Transformer, 455 KHz.: sim to AEPD 162B3277P17.	R122	19B800607P821	Metal film: 820 ohms + or -5%, 1/8 w.
			R123	19B800607P100	Metal film: 10 ohms + or -5%, 1/8 w.
L510	19A705470P13	Coil: 0.10 uH + or -20%.	R124	19B800607P471	Metal film: 470 ohms + or -5%, 1/8 w.
		TRANSISTORS	R125	19A702931P259	Metal film: 4020 ohms + or -1%, 200 VDCW, 1/8 w.
Q101	344A3225P1	Silicon, NPN: sim to MJF3055.	R126	19A702931P201	Metal film: 1000 ohms + or -1%, 200 VDCW, 1/8 w.
Q102	19A703197P2	Silicon, PNP; sim to MMBT4403 low profile.	R127	19A702931P262	Metal film: 4320 ohms + or -1%, 200 VDCW, 1/8 w.
Q102	19A703197P2		R128	19B800607P1	Metal film: Jumper.
Q103	13710431281	Silicon, PNP: sim to Motorola 2N4918. (Used in	R129	19B800607P153	Metal film: 15K ohms + or -5%, 1/8 w.
Q104	19A700076P2	Silicon, NPN: sim to MMBT3904, low profile.	R140 R141	19A702931P301 19A702931P210	Metal film: 10K ohms + or -1%, 200 VDCW, 1/8 w. Metal film: 1240 ohms + or -1%, 200 VDCW, 1/8 w.
Q105	19A700059P2	Silicon, PNP: sim to MMBT3906, low profile.	R142	19B800607P221	Metal film: 220 ohms + or -5%, 1/8 w.
Q201	19A704708P2	Silicon, NPN: sim to NEC 2SC3356.	13.142	102000077221	

PARTS LIST

SYMBOL	PART NO.	DESCRIPTION	SYMBOL	PART NO.	DESCRIPTION	1	SYMBOL	PART NO.	DESCRIPTION
R202	19B800607P101	Metal film: 100 ohms + or -5%, 1/8 w.	R403	19B800607P102			Z502	19A705613G42	Filter, Crystal.
R203	19B800607P560	Metal film: 56 ohms + or -5%, 1/8 w.	R404	19B800607P472	Metal film: 4.7K ohms + or -5%, 1/8 w.		Z503	19B801021P4	Filter, bandpass: 455 kHz; sim to Murata CFZM-455F.
R204	19B800607P221	Metal film: 220 ohms + or -5%, 1/8 w.	R405	19B800607P271	Metal film: 270 ohms + or -5%, 1/8 w.				
R205	19B800607P332	Metal film: 3.3K ohms + or -5%, 1/8 w.	R406	19B800607P471	Metal film: 470 ohms + or -5%, 1/8 w.				MISCELLANEOUS
R206	19B800607P222	Metal film: 2.2K ohms + or -5%, 1/8 w.	R501	19B800607P181	Metal film: 180 ohms + or -5%, 1/8 w.		13	19B801566P17	SHIELD.
R207	19B800607P181	Metal film: 180 ohms + or -5%, 1/8 w.	R502	19B800607P270	Metal film: 27 ohms + or -5%, 1/8 w.		14	19B801578P1	CLIP, SHIELD.
R208	19B800607P473	Metal film: 47K ohms + or -5%, 1/8 w.	R503	19B800607P472	Metal film: 4.7K ohms + or -5%, 1/8 w.				
R209	19B800607P332	Metal film: 3.3K ohms + or -5%, 1/8 w.	R504	19B800607P270	Metal film: 27 ohms + or -5%, 1/8 w.		<u> </u>		
and R210			R505	19B800607P683	Metal film: 68K ohms + or -5%, 1/8 w.				
R211	19B800607P101	Metal film: 100 ohms + or -5%, 1/8 w.	R506	19B800607P823	Metal film: 82K ohms + or -5%, 1/8 w.				
R213	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.	R507	19B800607P183	Metal film: 18K ohms + or -5%, 1/8 w.				
R214	19B800607P331	Metal film: 330 ohms + or -5%, 1/8 w.	R508	19B800607P1	Metal film: Jumper.				
R215	19B800607P822	Metal film: 8.2K ohms + or -5%, 1/8 w.	R509	19B800607P272	Metal film: 2.7K ohms + or -5%, 1/8 w.				
R216	19B800607P222	Metal film: 2.2K ohms + or -5%, 1/8 w.	R510	19B800607P270	Metal film: 27 ohms + or -5%, 1/8 w.				
R217	19B800607P101	Metal film: 100 ohms + or -5%, 1/8 w.	R511	19B800607P473	Metal film: 47K ohms + or -5%, 1/8 w.				
R218	19B800607P683	Metal film: 68K ohms + or -5%, 1/8 w.	R512	19B800607P822	Metal film: 8.2K ohms + or -5%, 1/8 w.				
R219	19B800607P273	Metal film: 27K ohms + or -5%, 1/8 w.	R513	19B800779P4	Variable: 1K ohms + or -25%, 100VDCW, .3 w.				
R221	19B800607P474	Metal film: 470K ohms + or - 5%, 1/8 w.	R514	19B800607P682	Metal film: 6.8K ohms + or -5%, 1/8 w.				
R222	19B800607P333	Metal film: 33K ohms + or -5%, 1/8 w.	R515	19B800607P821	Metal film: 820 ohms + or -5%, 1/8 w.				
R223	19B800607P105	Metal film: 1M ohms + or -5%, 1/8 w.							
R224	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.			INTEGRATED CIRCUITS				
R226	19B800779P4	Variable: 1K ohms + or -25%, 100VDCW, .3 w.	U101	19A705457P3	PA Module: 470-512 MHz; sim to M57704SH.				
R227	19B800607P473	Metal film: 47K ohms + or -5%, 1/8 w.	U102	19A134717P3	Linear: 8 Volt Regulator; sim to MC7808CT.				
R228	19B800607P223	Metal film: 22K ohms + or -5%, 1/8 w.	U103 and	19A701789P2	Linear: Dual Op Amp; sim to LM358.				
R229	19B800607P183	Metal film: 18K ohms + or -5%, 1/8 w.	U104						
R230	19B800607P332	Metal film: 3.3K ohms + or -5%, 1/8 w.	U105	RYT1246003/4	Sensor Temperature; sim to LM35.				
R231	19B800607P472	Metal film: 4.7K ohms + or -5%, 1/8 w.	U201	19D901958G5	Voltage Controlled Oscillator.				
R232	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.	U202	19A700029P44	Digital: BILATERAL SWITCH.				
R233	19B800607P332	Metal film: 3.3K ohms + or -5%, 1/8 w.	U203	19A704971P1	Linear: +5 Volt Regulator; sim to MC78L05ACP.				
R234	19B800607P472	Metal film: 4.7K ohms + or -5%, 1/8 w.	U204	19B801351P16	Crystal, Oscillator: 12.8 MHz.				
R235	19B800607P183	Metal film: 18K ohms + or -5%, 1/8 w.	U205	19A704287P2	Prescaler: /128, /129; sim to MC12018.				
R236	19B800607P471	Metal film: 470 ohms + or -5%, 1/8 w.	U206	19B800902P4	Digital: Synthesizer, CMOS Serial Input.				
R237	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.	U207	344A3820P1	Voltage Regulator: Linear, 8.5 Vdc.; sim to SGS 4885CX.				
thru R239			U501	19A704619P1	Linear: Osc/Mixer/IF/Det/Amp; sim to MC3361AP.				
R240	19B800607P154	Metal film: 150K ohms + or - 5%, 1/8 w.	U502	19A704073P2	Linear: 8 Volt Regulator; sim to MC78L08CP.				
thru R242			U503	344A3820P1	Voltage Regulator: Linear, 8.5 Vdc.; sim to SGS				
R245	19B800607P223	Metal film: 22K ohms + or -5%, 1/8 w.	0000	0111002011	4885CX.				
R246	19B800607P102	Metal film: 1K ohms + or -5%, 1/8 w.			CRYSTALS				
R249	19B800607P100	Metal film: 10 ohms + or -5%, 1/8 w.	Y501	19A705376P5	Crystal, Fixed Frequency: 45.455 MHz + or -10				
R251	19B800607P100	Metal film: 10 ohms + or -5%, 1/8 w.			PPM.				
thru R254									
R255	19B800779P16	Variable: 100K ohms + or -25%, 100 VDCW, .3 watt.	Z401 and	19A705458P10	FILTER, HELICAL: 485-505 MHz; sim to 302LXP-18065.				
R256	19B800607P103	Metal film: 10K ohms + or -5%, 1/8 w.	Z402	10000100501					
R401	19B801486P151	Metal film: 150 ohms + or -5%, 1/2 w.	Z403	19B801025P4	MIX, BALANCED; sim to Mini-Circuits SRA-1W.				
			Z501	19A705613G42	Filter, Crystal.				

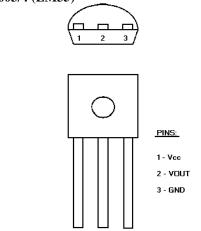
LBI-39017H IC DATA

RF POWER AMPLIFIER U101 19A705457P1 (M57704M (403-440 MHz) 19A705457P2 (M57794H (440-470 MHz) 19A705457P3 (M57704SH (470-512 MHz)

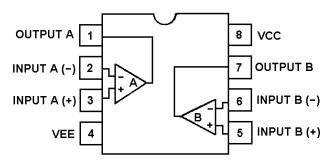


- 1. Pin
- 2. Vcc1 1ST STAGE
- 3. Vcc 2ND STAGE
- 4. Vcc OUTPUT STAGE
- 5. Pout
- 6. FIN GROUND

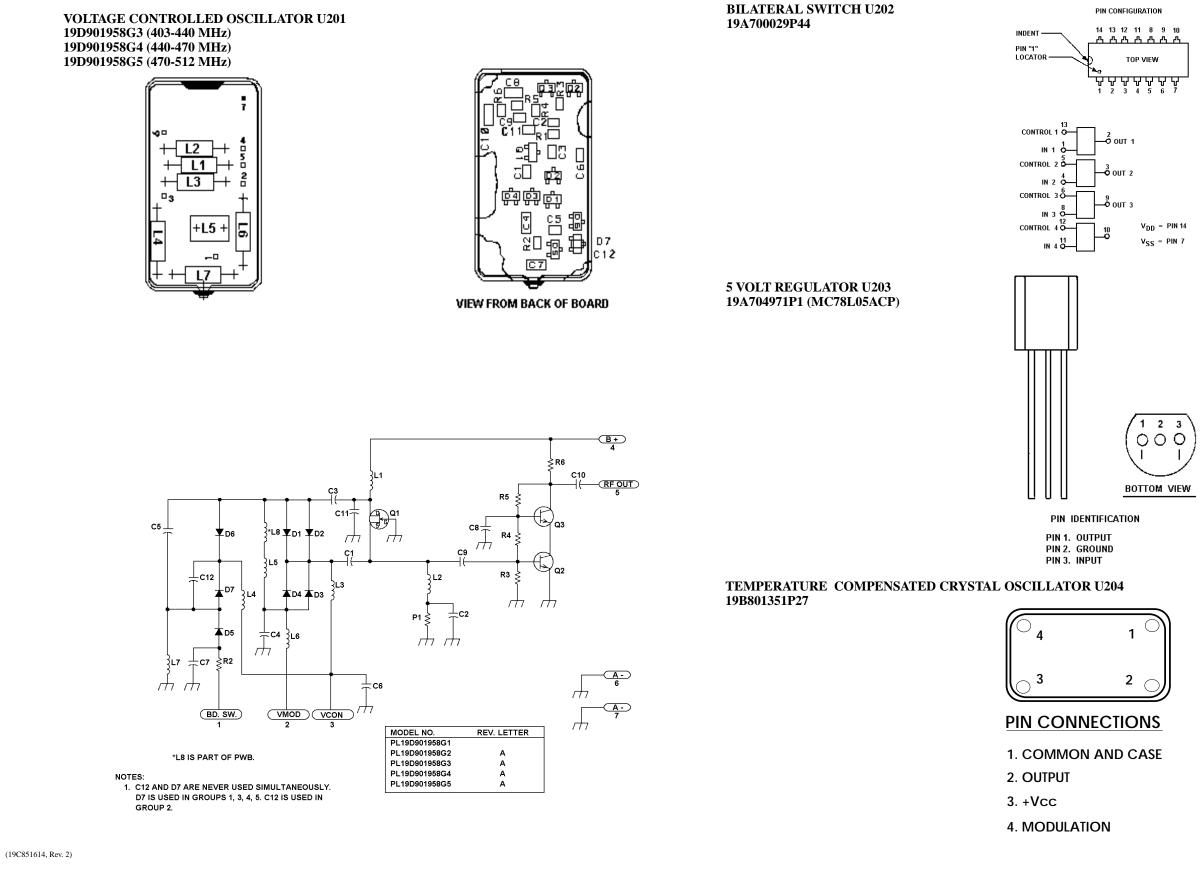
8 VOLT REGULATOR U102, U105 RYT1246003/4 (LM35)



DUAL OPERATIONAL AMPLIFIER U103 19A701789P2 (LM358)

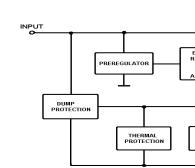


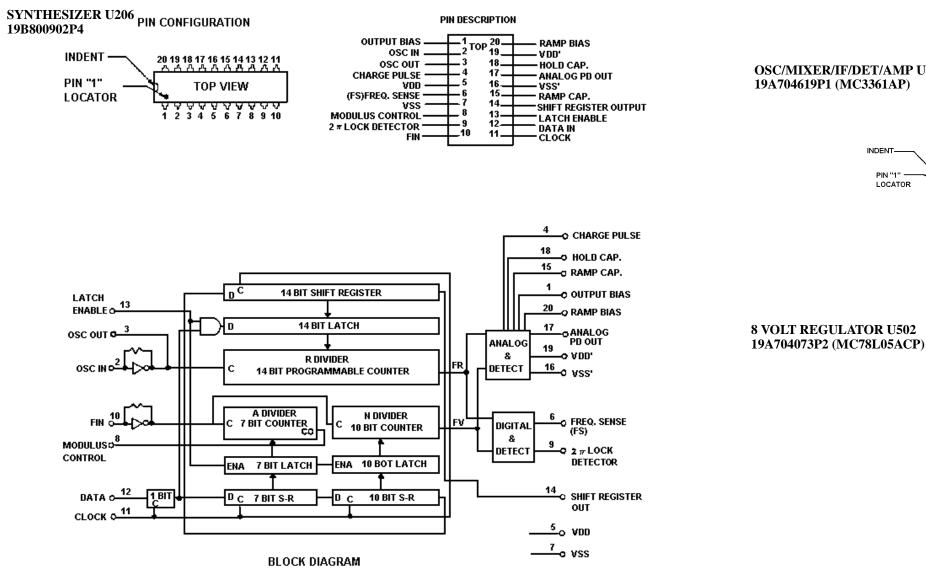
IC DATA & SCHEMATIC DIAGRAM



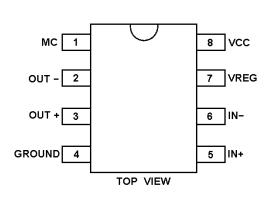
IC DATA





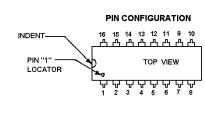


PRESCALER U205 19A704287P2



19B800902P4

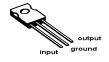
OSC/MIXER/IF/DET/AMP U501 19A704619P1 (MC3361AP)

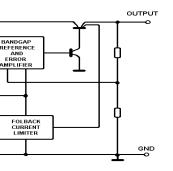


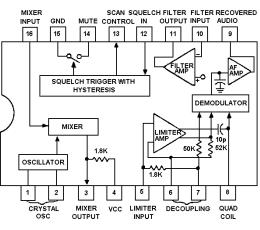


BOTTOM VIEW PIN 1 - OUTPUT PIN 2 - GROUND PIN 3 - INPUT

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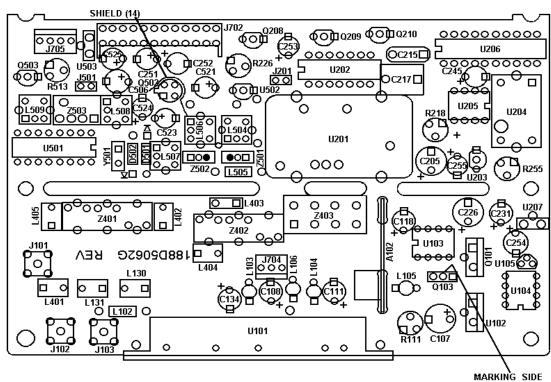
BLOCK DIAGRAM





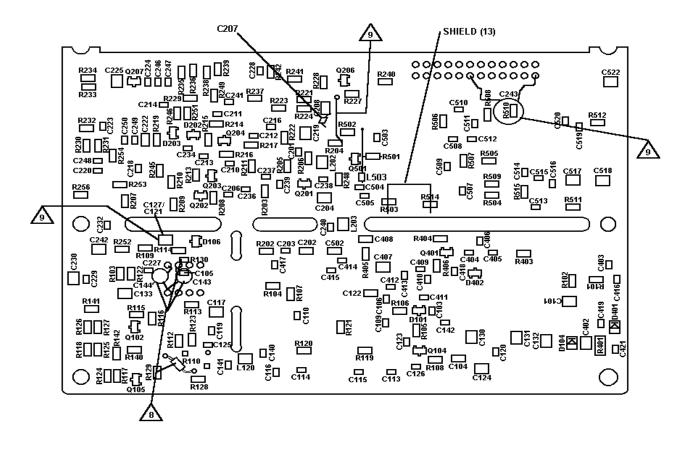
OUTLINE DIAGRAM

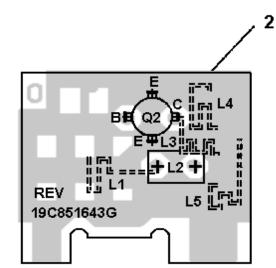
VIEW FROM SOLDER SIDE



VIEW FROM COMPONENT SIDE

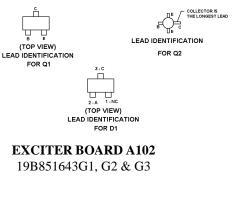
OF Q103





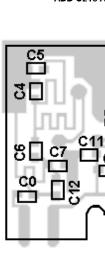
RF BOARD 188D5062G1-G3

(188D5062, Sh. 1, Rev. 7)





(19B851143, Rev. 1) (19A705441, Sh. 1, Rev. 0) (19A705441, Sh. 2, Rev. 1)

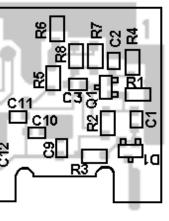


<u>/</u>8.

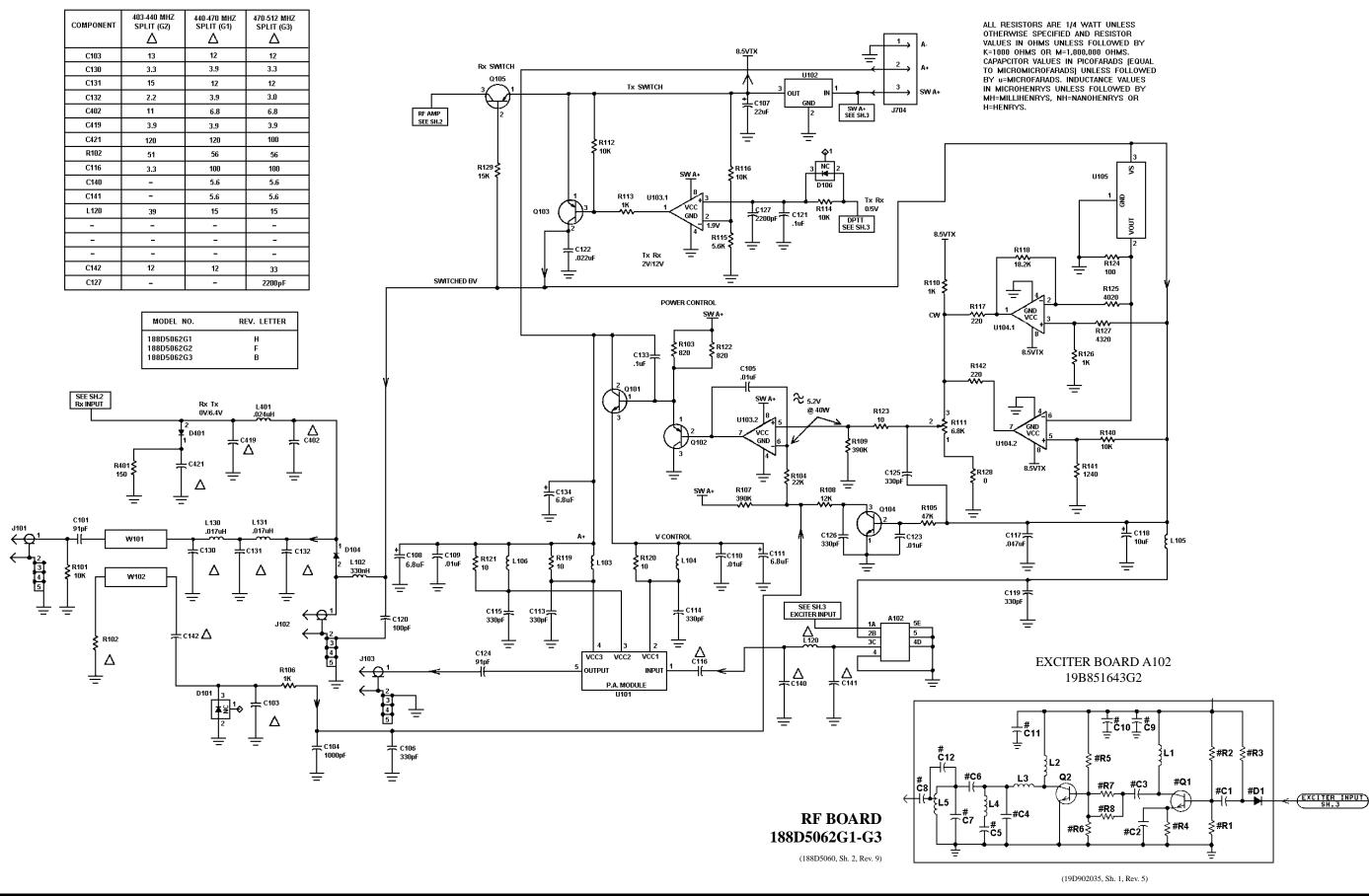
∕9.∖

HAND SOLDER R110 AS SHOWN.

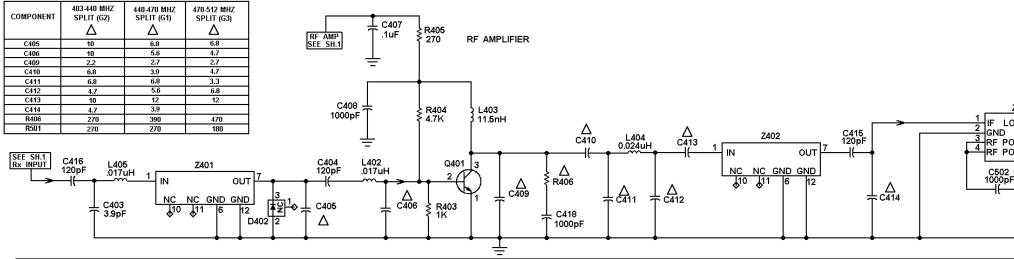
PIGGY BACK C127 ON C121 AS SHOWN AND HAND SOLDER. CUT RUN AT R204 WHERE SHOWN AND ADD JUMPER WIRE FROM R204 TO C253 AS SHOWN ADD C243 AS SHOWN.

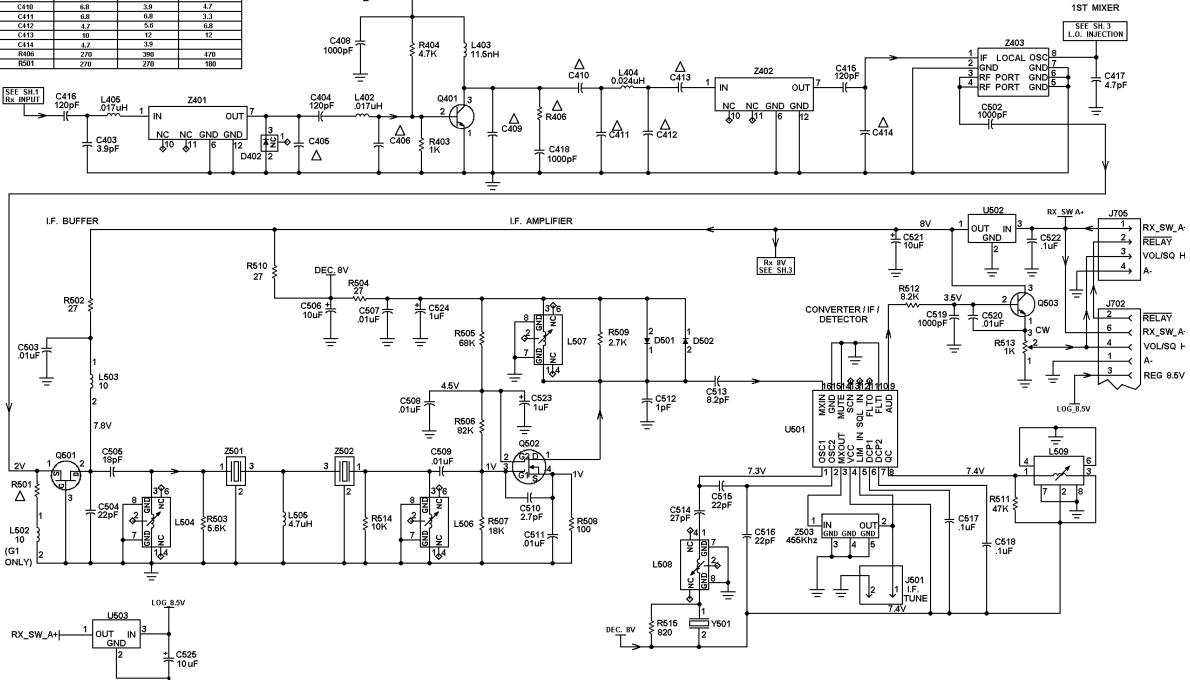


SCHEMATIC DIAGRAM



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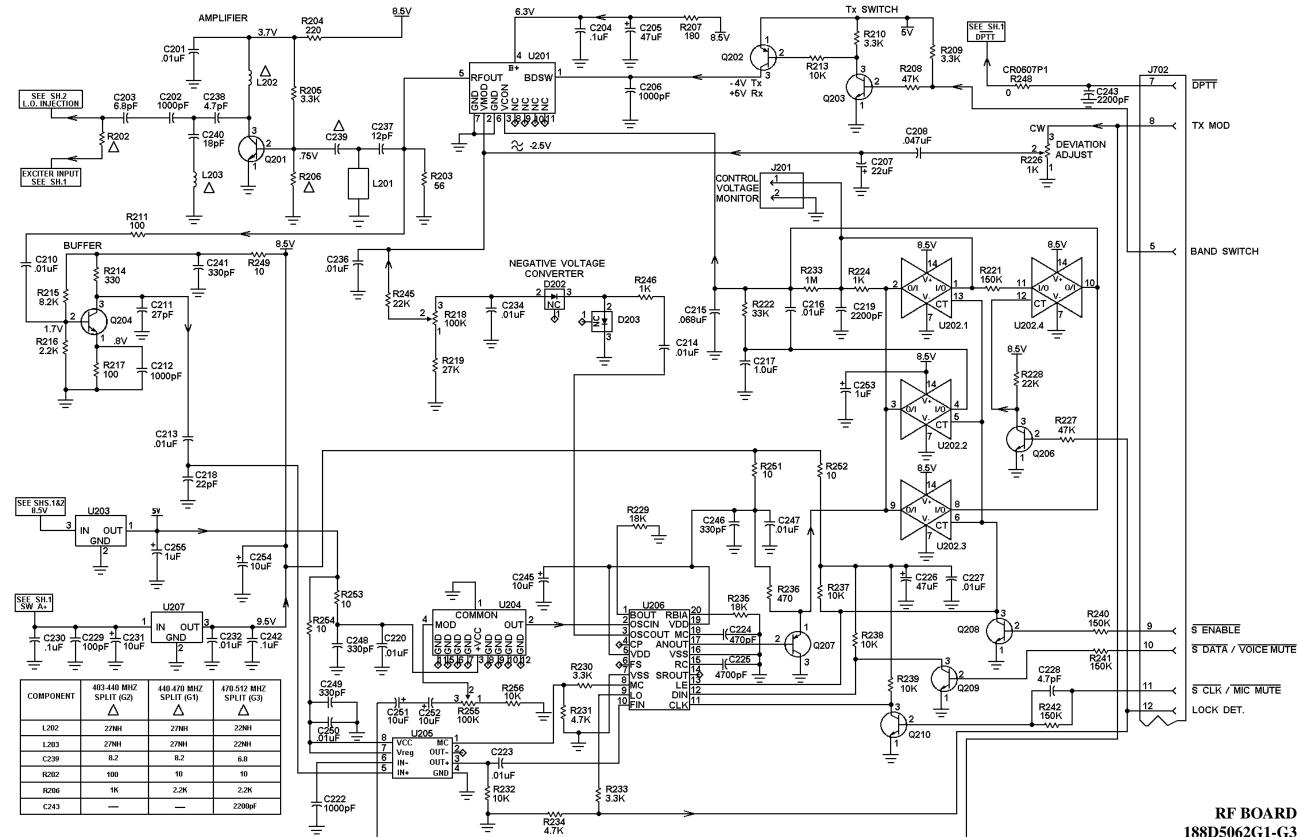


RF BOARD 188D5062G1-G3

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(188D5060, Sh. 2, Rev. 9)

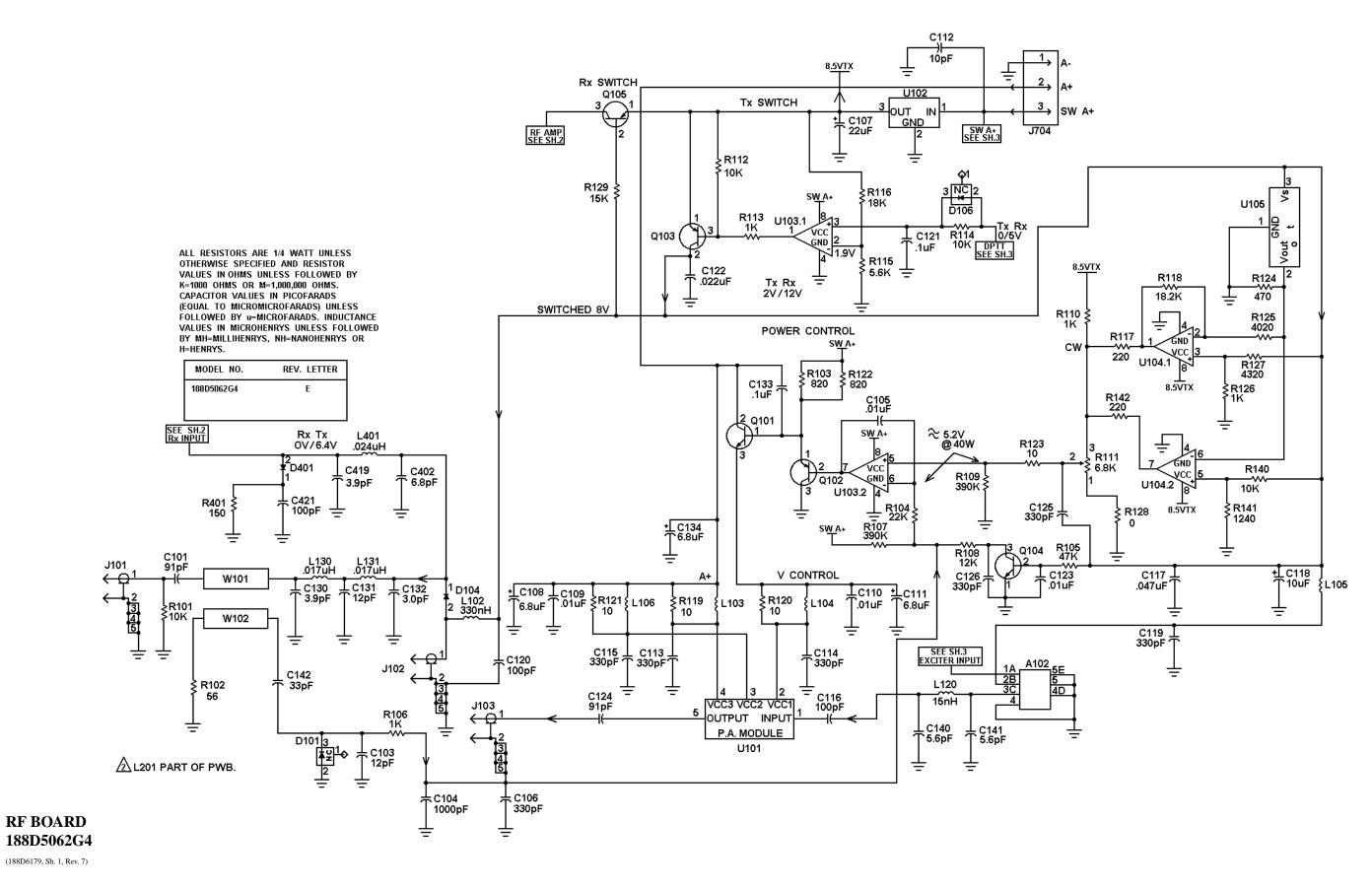
SCHEMATIC DIAGRAM



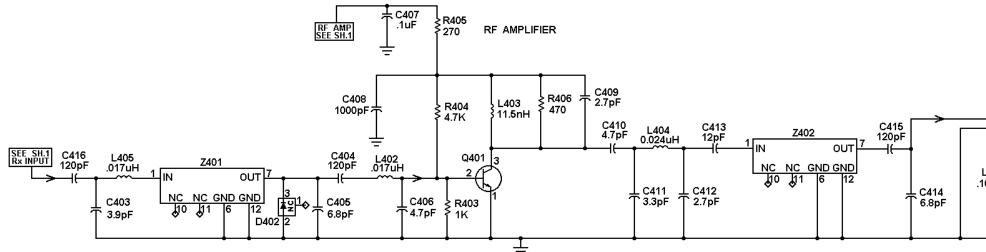
LBI-39017H

RF BOARD 188D5062G1-G3

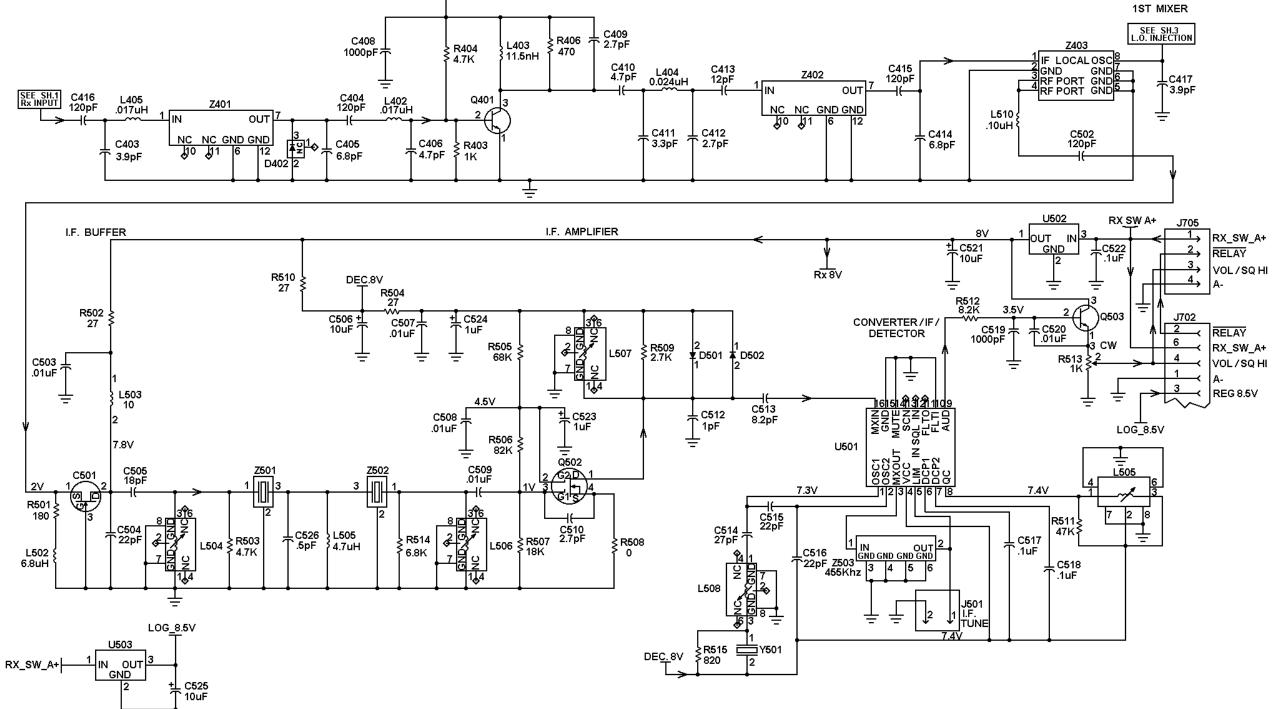
(188D5060, Sh. 3, Rev. 9)



SCHEMATIC DIAGRAM



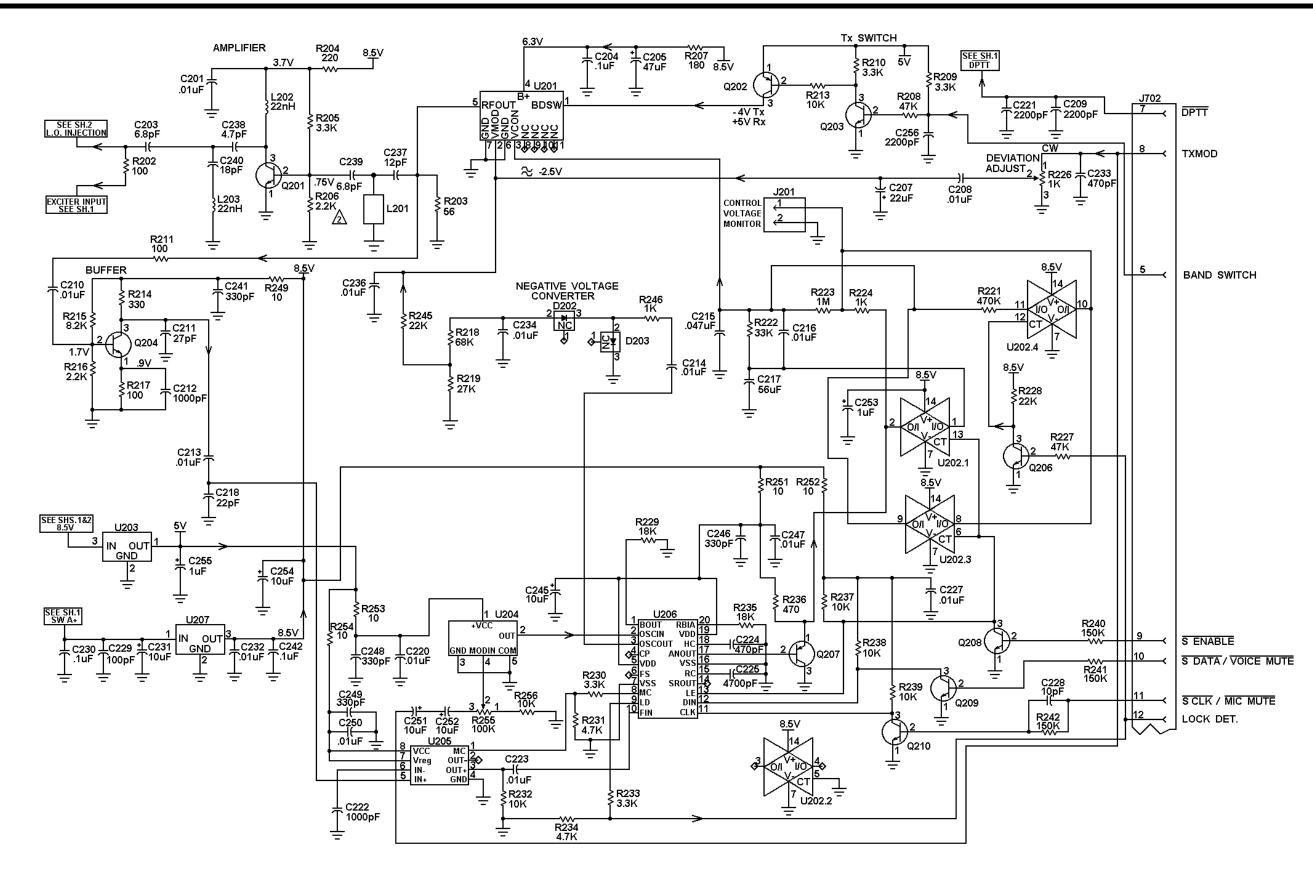
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RF BOARD 188D5062G4

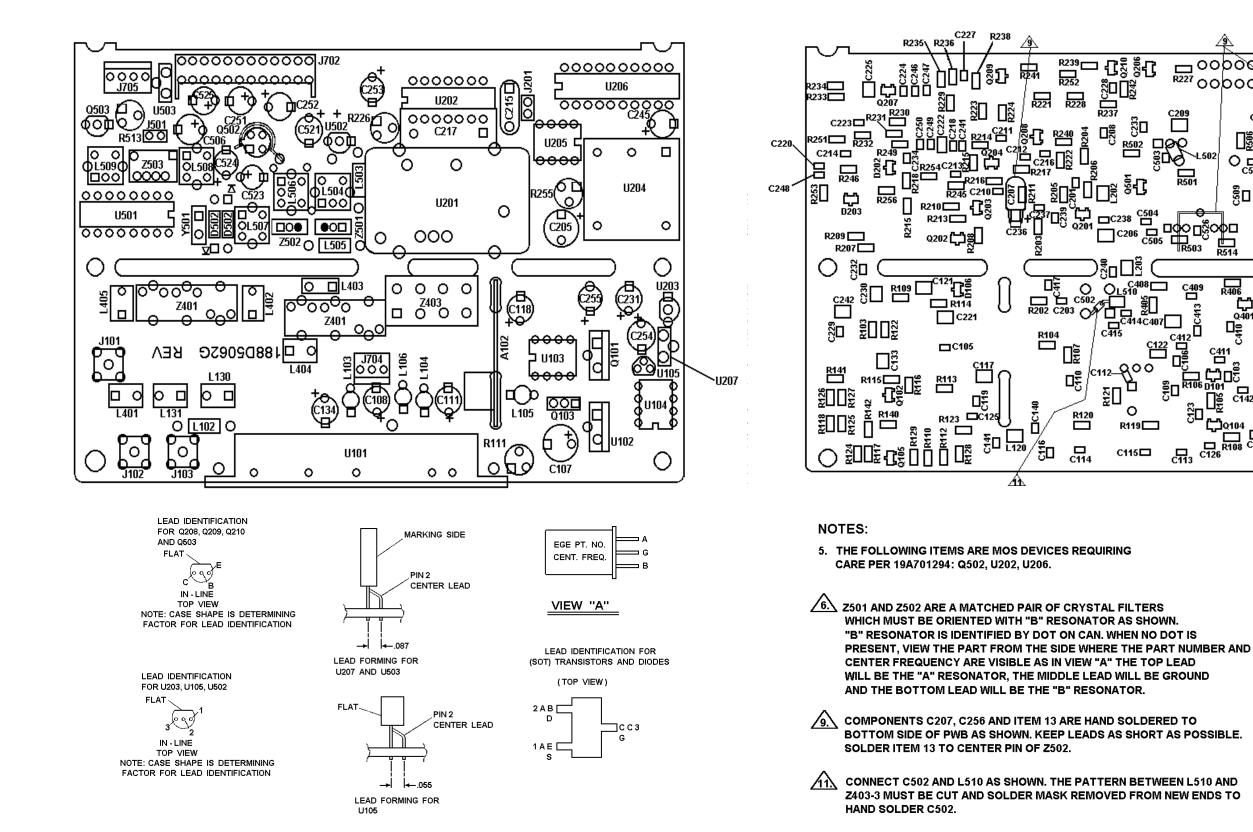
(188D6179, Sh. 2, Rev. 7)



RF BOARD 188D5062G4

(188D6179, Sh. 3, Rev. 7)

VIEW FROM COMPONENT SIDE



VIEW FROM SOLDER SIDE

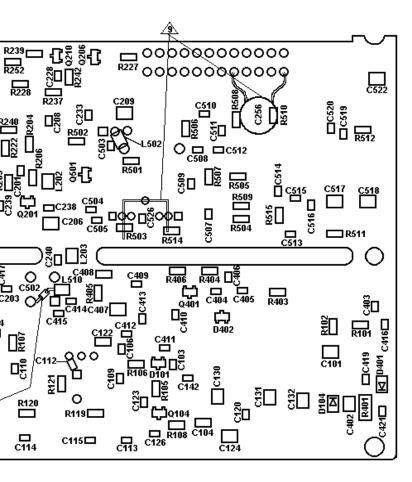
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R124

LBI-39017H







(188D5062, Sh. 2, Rev. 6)